

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HA12228F/HA12229F

Ordering Information

Operating Voltage

Product	Min	Max	Unit
HA12228F	6.5	12	V
HA12229F			

Note: 1. These ICs are designed to operate on single supply.

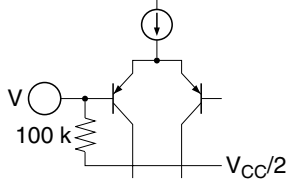
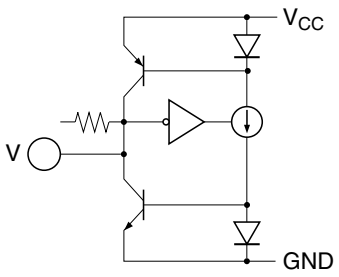
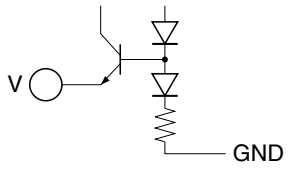
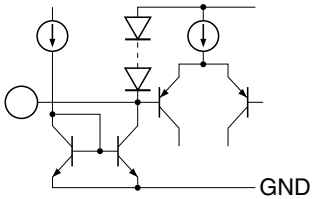
Standard Level

Product	Package	PB-OUT Level
HA12228F	FP-40B	300 mVrms
HA12229F		

Function

Product	PB-EQ	Music Sensor	Mute	Dolby B-NR
HA12228F	○	○	○	○
HA12229F	○	○	○	×

Pin Description, Equivalent Circuit ($V_{cc} = 9\text{ V}$ single supply, $T_a = 25^\circ\text{C}$, No Signal, The value in the table shows typical value.)

Pin No.	Terminal Name	Note	Equivalent Circuit	Description
13	MSI	$V = V_{cc}/2$		MS input *1
4	TAI(L)			Tape input
27	TAI(R)			
23 *2	DET(R)	$V = 2.5\text{ V}$		Time constant pin for NR rectifier
8 *2	DET(L)			
26	RIP	$V = V_{cc}/2$		Ripple filter
5 *3	Bias	$V = 0.28\text{ V}$		Dolby bias current input
14	MSDET	—		Time constant pin for MS rectifier *1

- Notes: 1. MS: Music Sensor
 2. Non connection regarding HA12229F.
 3. Test pin regarding HA12229F. Usually open or pull down to GND with 18 kΩ.

HA12228F/HA12229F

Pin Description, Equivalent Circuit ($V_{CC} = 9\text{ V}$ single supply, $T_a = 25^\circ\text{C}$, No Signal, The value in the table shows typical value.) (cont.)

Pin No.	Terminal Name	Note	Equivalent Circuit	Description
25	PBOUT(R)	$V = V_{CC}/2$		PB output
6	PBOUT(L)			
12	MAOUT			MS amp. output *1
29	EQOUT(R)	$V = V_{CC}/2$		Equalizer output
2	EQOUT(L)			
30	M-OUT(R)	$V = V_{CC}/2$		Equalizer output for time constant
1	M-OUT(L)			
37	FIN(R)	—		Equalizer input (FORWARD)
39	FIN(L)			
35	RIN(R)	—		Equalizer input (REVERSE)
33	RIN(L)			

Note: 1. MS: Music Sensor

Pin Description, Equivalent Circuit ($V_{cc} = 9\text{ V}$ single supply, $T_a = 25^\circ\text{C}$, No Signal, The value in the table shows typical value.) (cont.)

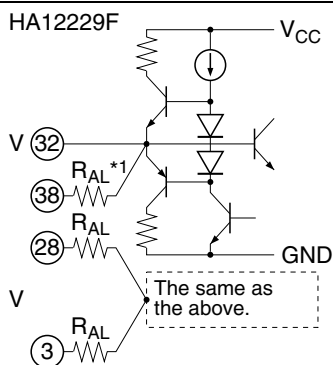
Pin No.	Terminal Name	Note	Equivalent Circuit	Description
20	MUTE ON/OFF	—		Mode control input
21 *1	NR ON/OFF			
19	120/70			
17	F/R			
18	S/R(MS G_v)			
16	MSOUT	—		MS output (to MPU) *2
10	MS G_v (S)	$V = V_{cc}/2$		MS gain terminal *2
11	MS G_v (R)			
31	NFI(R)	$V = V_{cc}/2$		Equalizer output for time constant
40	NFI(L)			

Notes: 1. Non connection regarding HA12229F.
 2. MS: Music Sensor

HA12228F/HA12229F

Pin Description, Equivalent Circuit ($V_{CC} = 9\text{ V}$ single supply, $T_a = 25^\circ\text{C}$, No Signal, The value in the table shows typical value.) (cont.)

Pin No.	Terminal Name	Note	Equivalent Circuit	Description
32	VREF1	$V = V_{CC}/2$		Reference output
38	VREF2			
28	VREF3			
3	VREF4			

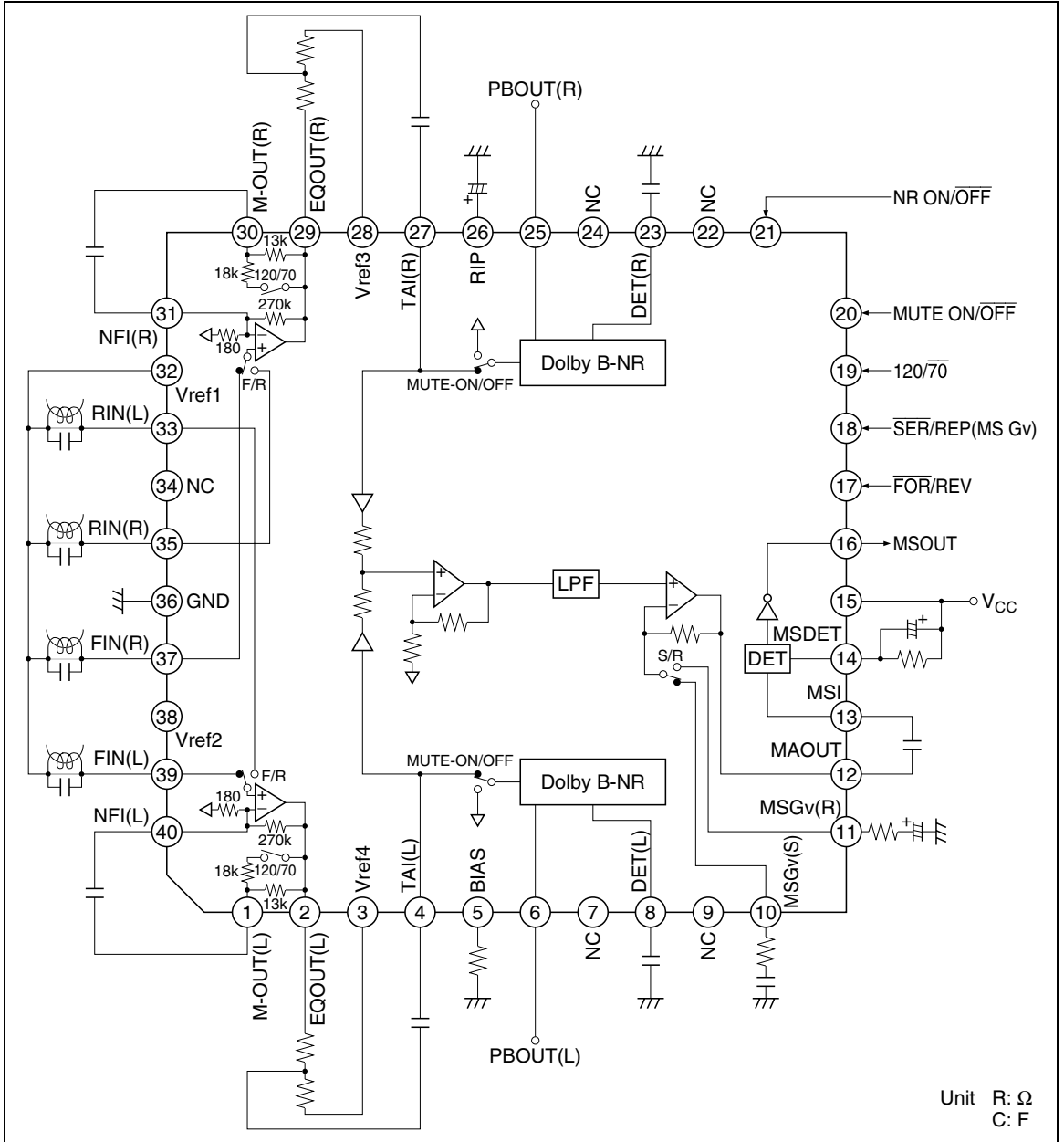


15	V_{CC}	—		V_{CC} pin
36	GND	—		GND pin
7	NC	—		
9				
22				
24				
34				

Note: 1. R_{AL} : Parasitic metal resistance

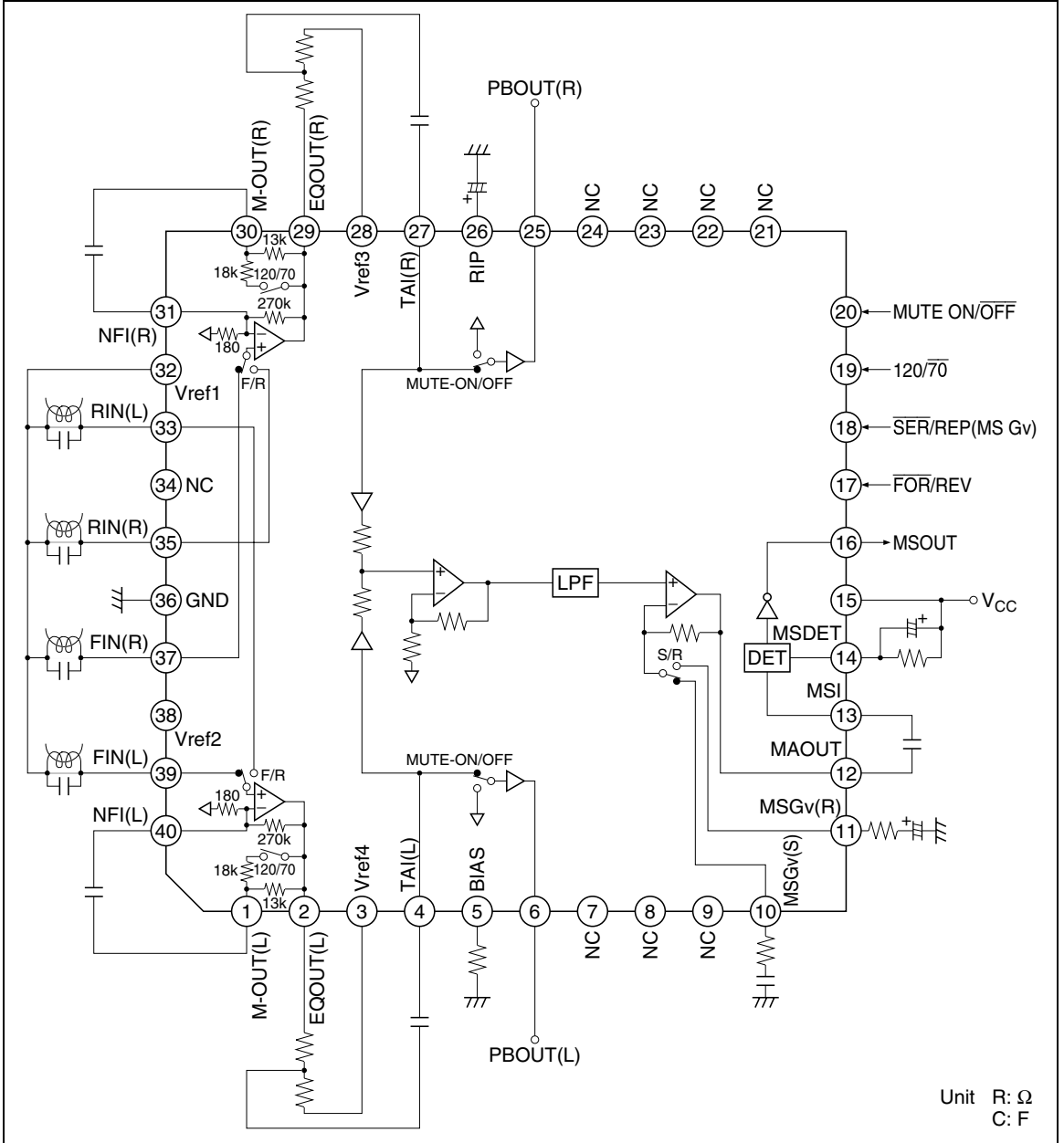
Block Diagram

HA12228F



HA12228F/HA12229F

HA12229F



Functional Description

Power Supply Range

HA12228F/HA12229F are provided with three line output level, which will permit on optimum overload margin for power supply conditions. And these are designed to operate on single supply only.

Table 1 Supply Voltage Range

Product	Single Supply
HA12228F	6.5 V to 12.0 V
HA12229F	

Note: The lower limit of supply voltage depends on the line output reference level.
The minimum value of the overload margin is specified as 12 dB by Dolby Laboratories.

Reference Voltage

These devices provide the reference voltage of half the supply voltage that is the signal grounds. As the peculiarity of these devices, the capacitor for the ripple filter is very small about 1/100 compared with their usual value. The block diagram is shown as figure 1.

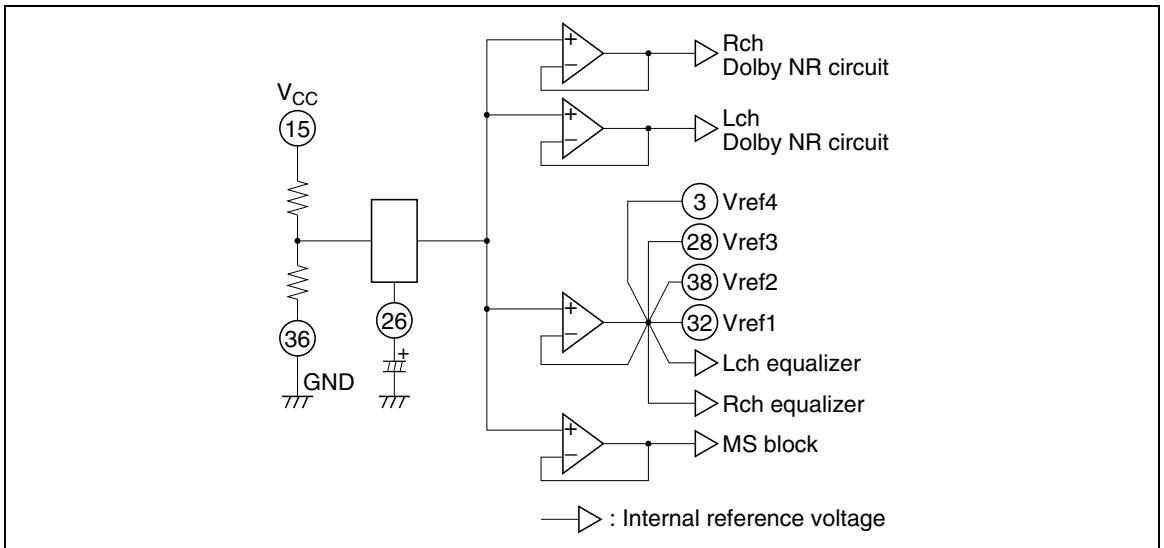


Figure 1a The HA12228F Block Diagram of Reference Supply Voltage

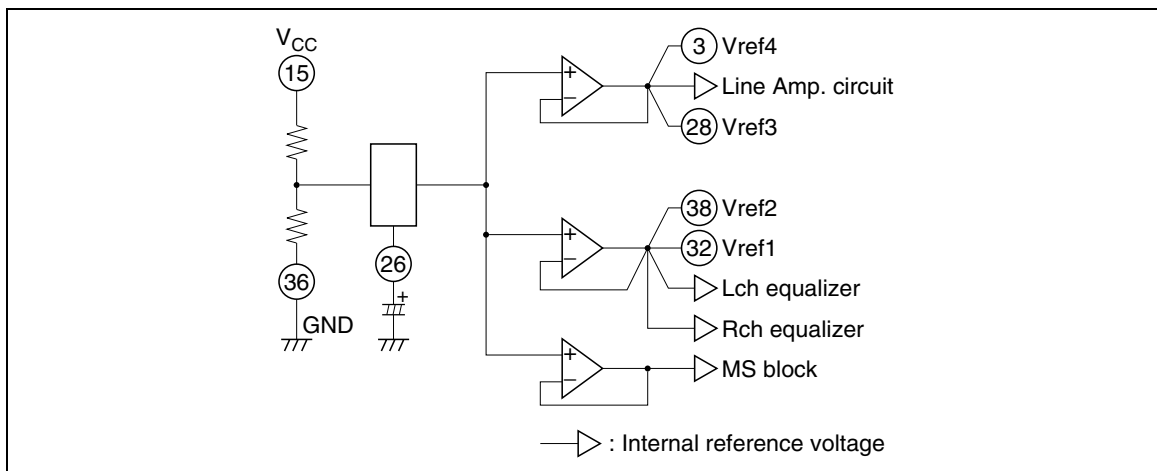


Figure 1b The HA12229F Block Diagram of Reference Supply Voltage

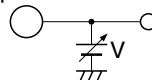
Operating Mode Control

HA12228F/HA12229F provides fully electronic switching circuits. And each operating mode control are controlled by parallel data (DC voltage).

When a power supply of this IC is cut off, for a voltage, in addition to a mode control terminal even though as do not destruct it, in series for resistance.

Table 2 Threshold Voltage (V_{TH})

Pin No.	Lo	Hi	Unit	Test Condition
17, 18, 19, 20, 21*	-0.2 to 1.0	3.5 to V_{CC}	V	Input Pin Measure



Note: * Non connection regarding HA12229F.

Table 3 Switching Truth Table

Pin No.	Pin Name	Lo	Hi
17	Forward/Reverse	Forward	Reverse
18	Search/Repeat	Search (FF or REV)	Repeat (Normal speed)
19	120 μ/70 μ	70 μ (Metal or Chrome)	120 μ (Normal)
20	MUTE ON/OFF	MUTE-OFF	MUTE-ON
21*	NR ON/OFF	NR-OFF	NR-ON

Notes: * Non connection regarding HA12229F.

1. Each pins are on pulled down with 100 kΩ internal resistor. Therefore, it will be low-level when each pins are open.
2. Over shoot level and under shoot level of input signal must be the standardized. (High: V_{cc}, Low: -0.2 V)
3. Reducing pop noise is so much better for 10 kΩ to 22 kΩ resisitor and 1 μF to 22 μF capacitor shown figure 2.

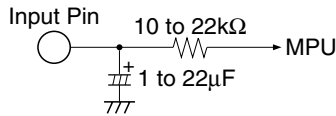


Figure 2 Interface for Reduction of Pop Noise

Input Block Diagram and Level Diagram

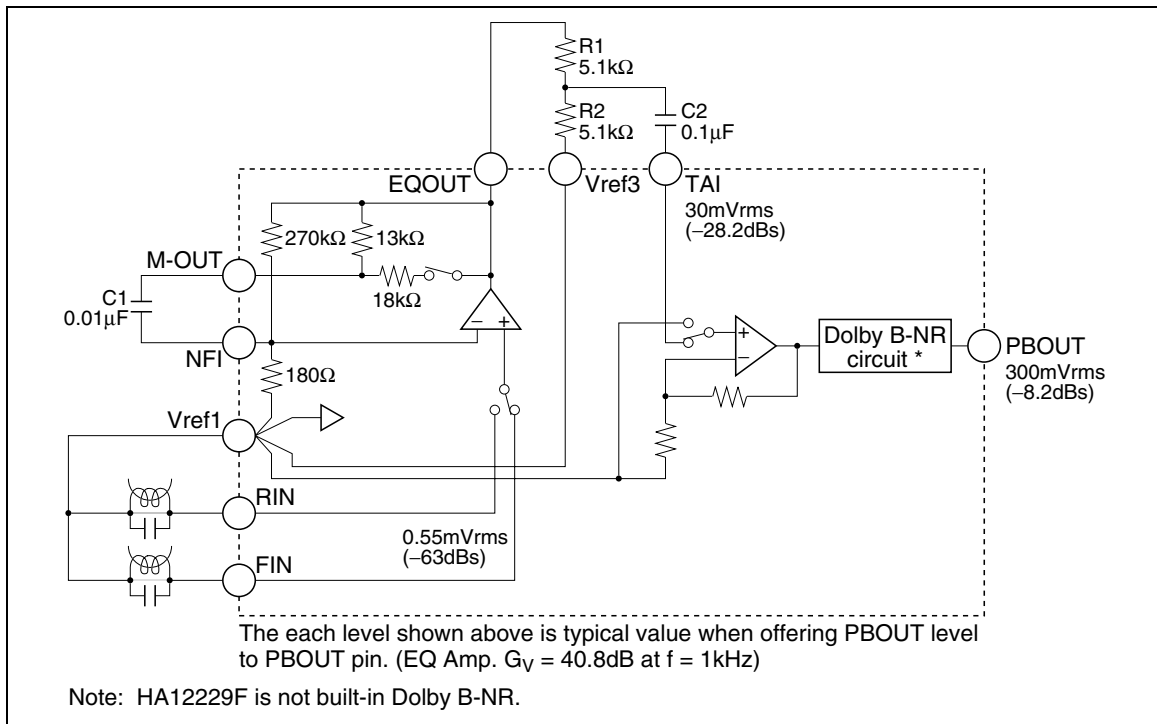


Figure 3 Input Block Diagram

Adjustment of Playback Dolby Level

After replace R5 and R6 with a half-fix volume of 10 kΩ, adjust playback Dolby level.

The Sensitivity Adjustment of Music Sensor

Adjusting MS Amp. gain by external resistor, the sensitivity of music sensor can set up. The music sensor block diagram is shown in figure 4, and frequency response is shown in figure 5.

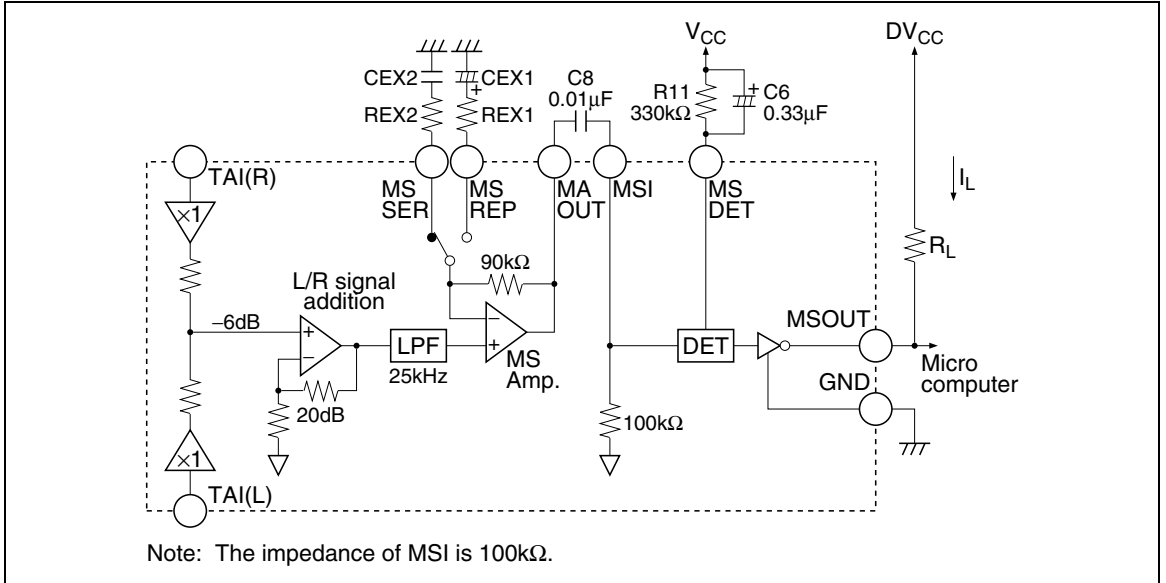


Figure 4 Music Sensor Block Diagram

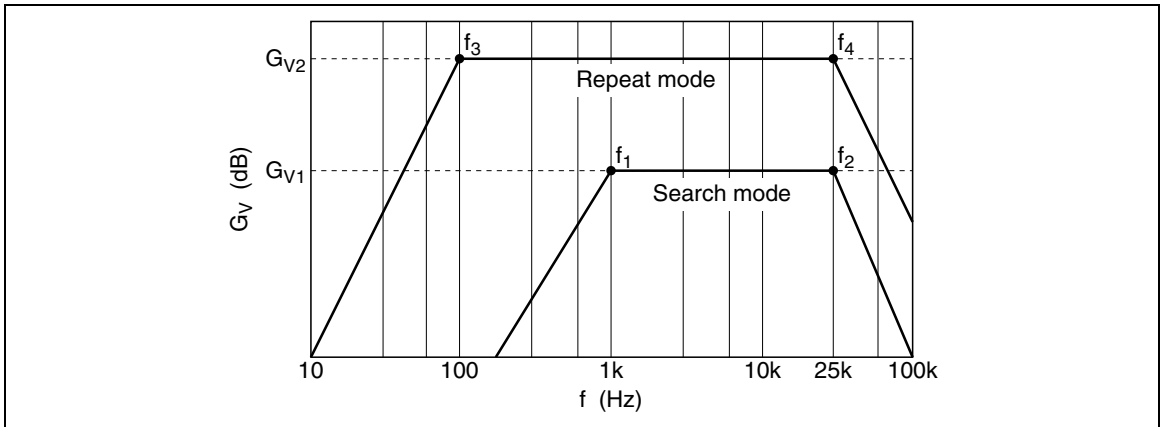


Figure 5 Frequency Response

1. Search mode

$$G_{V1} = 20\text{dB} + 20 \log \left(1 + \frac{90\text{k}}{\text{REX2}} \right) \text{ [dB]}$$

$$f_1 = \frac{1}{2\pi \cdot \text{CEX2} \cdot \text{REX2}} \text{ [Hz]}, \quad f_2 = 25\text{k} \text{ [Hz]}$$

2. Repeat mode

$$G_{V2} = 20\text{dB} + 20 \log \left(1 + \frac{90\text{k}}{\text{REX1}} \right) \text{ [dB]}$$

$$f_3 = \frac{1}{2\pi \cdot \text{CEX1} \cdot \text{REX1}} \text{ [Hz]}, \quad f_4 = 25\text{k} \text{ [Hz]}$$

G_{VIA} : L-R signal addition circuit gain.

The sensitivity of music sensor (S) is computed by the formula mentioned below.

$$S = - \left(G_{V1}^{*1} - 20 \log \frac{130^{*3}}{30^{*2}} \right) = 12.7 - G_V \text{ [dB]}$$

Note: 1. Search mode: G_{V1} , Repeat mode: G_{V2}

2. Standard level of TAI pin (Dolby level correspondence) = 30 mVrms

3. Standard sensing level of music sensor = 130 mVrms

Item	REX1, 2	CEX1, 2	$G_{V1,2}$	$f_{1,3}$	$f_{2,4}$	S (one side channel)	S (both channel)
Search mode	24 k Ω	0.01 μ F	33.5 dB	663 Hz	25 kHz	-14.8 dB	-20.8 dB
Repeat mode	2.4 k Ω	1 μ F	51.7 dB	66.3 Hz	25 kHz	-33.0 dB	-39.0 dB

Note: S is 6 dB down in case of one-side channel. And this MS presented hysteresis lest MSOUT terminal should turn over again High level or Low level, in case of thresh S level constantly.

Music Sensor Time Constant

1. Sensing no signal to signal (Attack) is determined by C6, 0.01 μ F to 1 μ F capacitor C6 can be applicable.
2. Sensing signal to no signal (Recovery) is determined by C6 and R11, however preceding (1), 100 k Ω to 1 M Ω can be applicable.

Music Sensor Output (MSOUT)

As for the internal circuit of music sensor block, music sensor output pin is connected to the collector of NPN type directly, therefore, output level will be “high” when sensing no signal. And output level will be “low” when sensing signal.

$$I_L = \frac{DV_{CC} - \text{MSOUT}_{LO}^*}{R_L}$$

* MSOUT_{LO} : Sensing signal (about 1V)

Note: 1. Supply voltage of MSOUT pin must be less than V_{CC} voltage.

The Tolerances of External Components for Dolby NR (Only HA12228F)

For adequate Dolby NR tracking response, take external components shown below.
 Also, leak is small capacity, and please employ a good quality object.

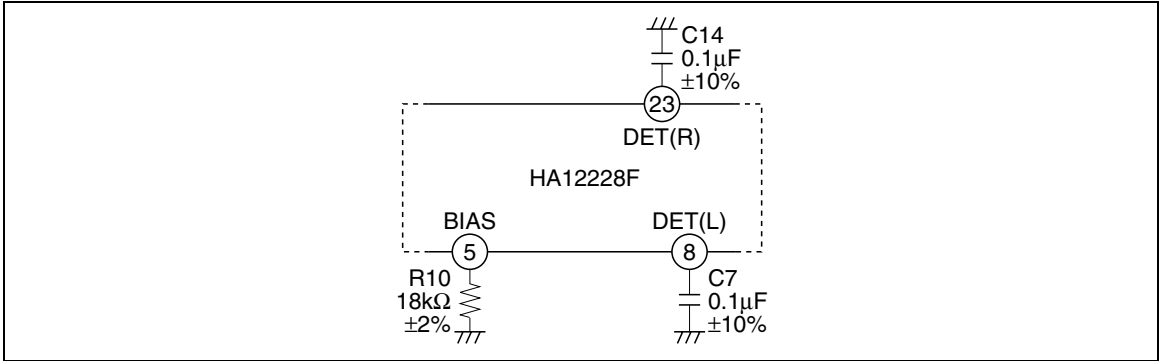
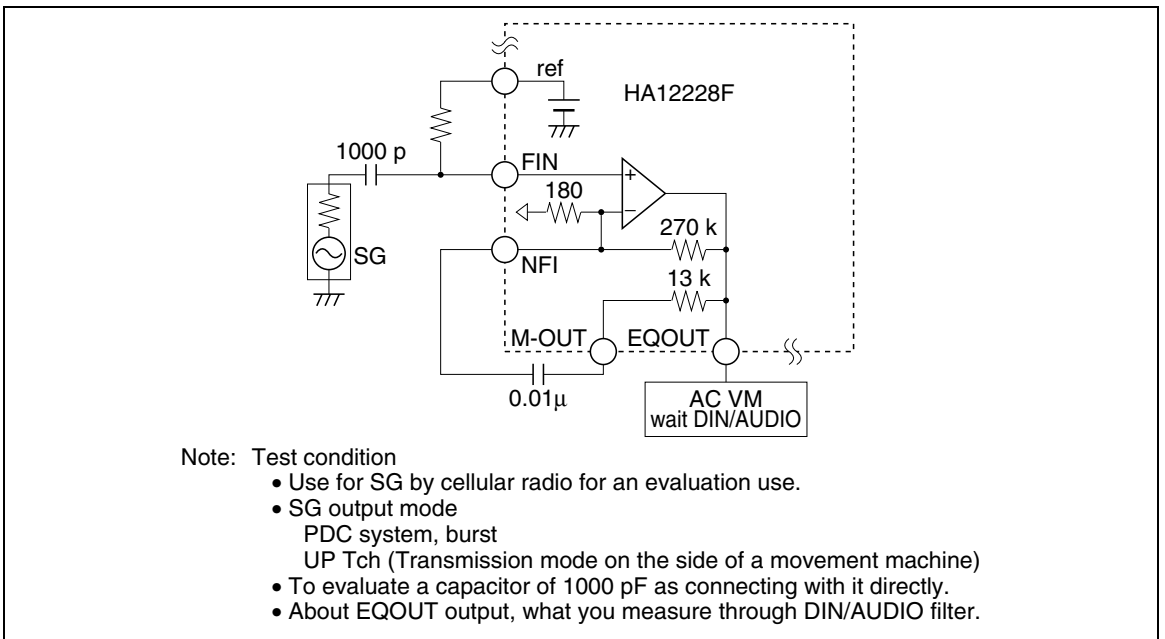


Figure 6 Tolerance of External Components

Countermeasure of a Cellular Phone Noise

This IC have reinforced a cellular phone noise countermeasure, to show it hereinafter.
 However, it is presumed that this effect change it greatly, by a mount set.
 Please sufficiently examine an arrangement of positions, shield method, wiring pattern, in order to obtain a maximum effect.
 A high terminal of a noise sensitivity of this IC is FIN, RIN, NFI and RIP.



- Note: Test condition
- Use for SG by cellular radio for an evaluation use.
 - SG output mode
 PDC system, burst
 UP Tch (Transmission mode on the side of a movement machine)
 - To evaluate a capacitor of 1000 pF as connecting with it directly.
 - About EQOUT output, what you measure through DIN/AUDIO filter.

Figure 7 Test Circuit

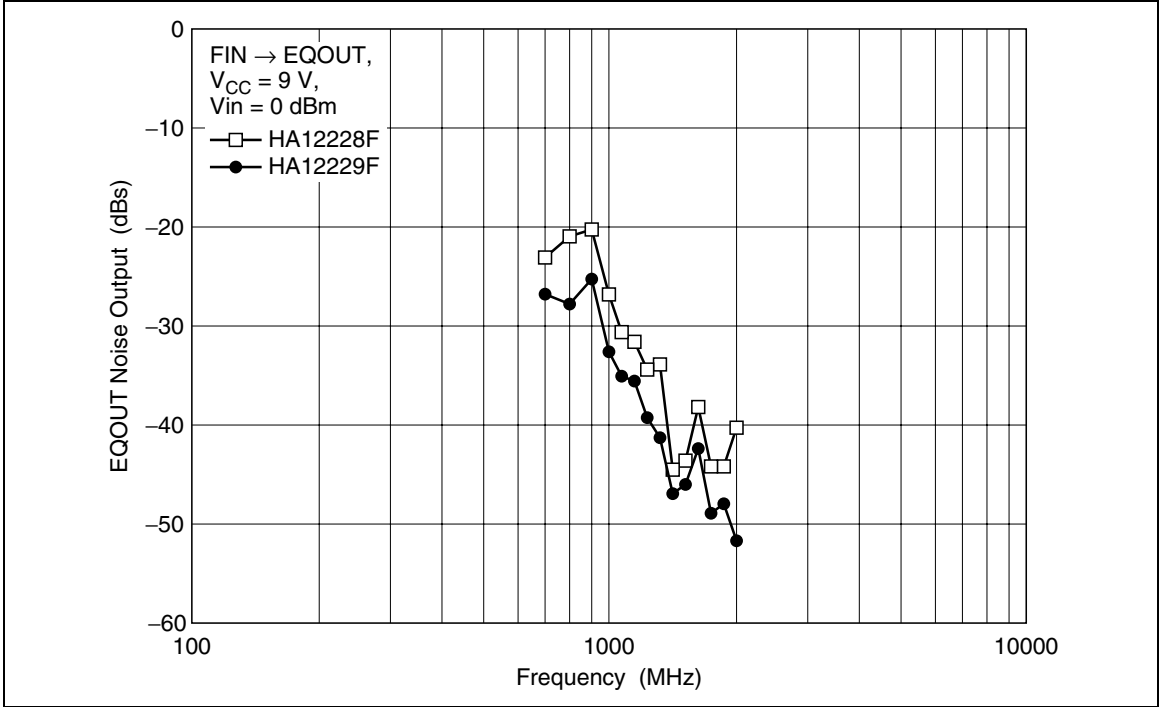


Figure 8 EQOUT Noise Output vs. Transmission Frequency Characteristic

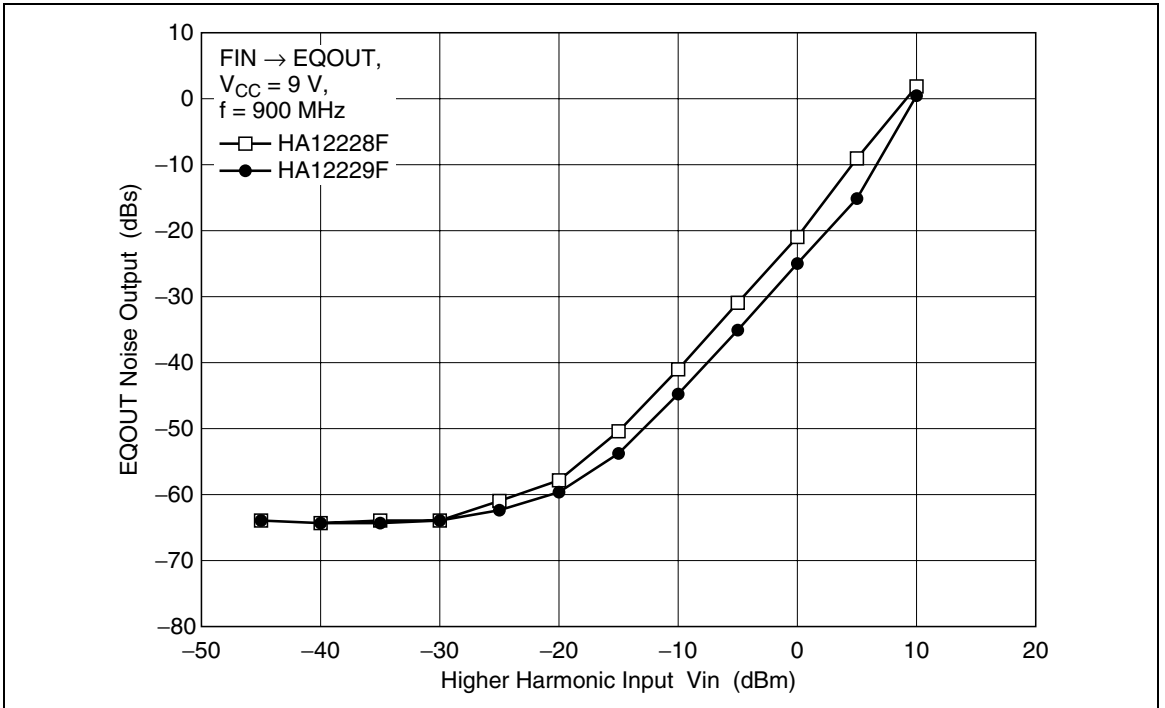


Figure 9 EQOUT Noise Output vs. Transmission Signal Input Level Characteristic

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Rating	Unit	Note
Maximum supply voltage	V_{cc} Max	16	V	
Power dissipation	P_d	400	mW	$T_a \leq 85^\circ\text{C}$
Operating temperature	T_{opr}	-40 to +85	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$	

Electrical Characteristics

HA12228F

(T_a = 25°C, V_{CC} = 9 V, Dolby level 0 dB = PBOUT level 0 dB = 300 mVrms, EQOUT level 0 dB = 60 mVrms)

Item	Symbol	Test Condition										Specification				Application Terminal					
		IC Condition					Test Condition					Input		Output		Terminal					
		NR ON/OFF	MUTE ON/OFF	120μ/70μ	SER/REP	FOR/REV	f _{in} (Hz)	PBOUT level (dB)	EQOUT level (dB)	Other	Min	Typ	Max	Unit	R	L	R	L	COM	Remark	
Quiescent current	I _Q	OFF	OFF	70μ	SER	FOR	—	—	—	—	1k	0	—	4.0	9.5	15.0	mA	—	—	—	15
Input Amp. gain	G _v /A	OFF	OFF	—	—	—	—	—	—	—	2k	-20	—	19.0	20.0	21.0	dB	27	4	25	6
B-type decode cut	DEC 2k (1)	ON	OFF	—	—	—	—	—	—	—	2k	-30	—	-5.8	-4.3	-2.8	dB	27	4	25	6
	DEC 2k (2)	ON	OFF	—	—	—	—	—	—	—	2k	-30	—	-10.0	-8.5	-7.0	dB	27	4	25	6
	DEC 5k (1)	ON	OFF	—	—	—	—	—	—	—	5k	-20	—	-4.7	-3.2	-1.7	dB	27	4	25	6
PBOUT offset	DEC 5k (2)	ON	OFF	—	—	—	—	—	—	—	5k	-30	—	-9.7	-8.2	-6.7	dB	27	4	25	6
	Vofs	OFF	OFF→ON	—	—	—	—	—	No signal	—	—	—	—	-15.0	0	15.0	mV	—	—	25	6
Signal handling	V _o max	ON	OFF	—	—	—	—	—	THD=1%	—	1k	—	—	12.0	13.0	—	dB	27	4	25	6
Signal to noise ratio	S/N	ON	OFF	—	—	—	—	(0)	Rg=10kΩ, CCIR/ARM	—	1k	0	—	70.0	80.0	—	dB	27	4	25	6
Total Harmonic Distortion	THD	ON	OFF	—	—	—	—	0	—	—	1k	0	—	—	0.05	0.3	%	27	4	25	6
Channel separation	CTRL (1)	—	—	—	—	—	—	—	—	—	1k	—	(+20)	50.0	60.0	—	dB	37	39	29→2	2→29
MUTE attenuation	CTRL (2)	OFF	OFF	—	—	—	—	—	—	—	1k	(+12)	—	70.0	80.0	—	dB	27	4	25→6	6→25
	CT MUTE	OFF	OFF→ON	—	—	—	—	(+12)	—	—	1k	(+12)	—	70.0	80.0	—	dB	27	4	25	6
PB-EQ gain	G _v EQ 1k	—	—	120μ	—	FOR/REV	—	—	—	—	1k	—	0	37.8	40.8	43.8	dB	37/35	39/33	29	2
	G _v EQ 10k(1)	—	—	120μ	—	FOR	—	—	—	—	10k	—	0	33.9	36.9	39.9	dB	37	39	29	2
	G _v EQ 10k(2)	—	—	70μ	—	FOR	—	—	—	—	10k	—	0	29.6	32.6	35.6	dB	37	39	29	2
PB-EQ Maximum output level	V _{OM}	—	—	120μ	—	FOR	—	—	THD=1%	—	1k	—	—	300	600	—	mVrms	37	39	29	2
PB-EQ T.H.D.	THD-EQ	—	—	120μ	—	FOR/REV	—	—	+14dB	—	1k	—	—	—	0.1	0.3	%	37/35	39/33	29	2
PB-EQ input conversion noise	V _N	—	—	120μ	—	FOR/REV	—	—	Rg=680Ω, DIN-AUDIO	—	(1k)	—	—	—	0.7	1.5	μVrms	37/35	39/33	29	2
MS sensing level	V _{ON} (1)	OFF	OFF	—	SER	—	—	—	—	—	5k	—	—	-36.0	-32.0	-28.0	dB	27	4	25	6
	V _{ON} (2)	OFF	OFF	—	REP	—	—	—	—	—	5k	—	—	-18.0	-14.0	-10.0	dB	27	4	25	6
MS output low level	V _{OL}	OFF	OFF	—	SER	—	—	0	—	—	5k	—	—	—	1.0	1.5	V	27	4	—	—
MS output leakage current	I _{OH}	—	—	—	—	—	—	—	No signal	—	—	—	—	—	0.0	2.0	μA	—	—	—	—
Control voltage	V _{IL}	—	—	—	—	—	—	—	—	—	—	—	—	-0.2	—	—	V	—	—	—	17 to 21
	V _{IH}	—	—	—	—	—	—	—	—	—	—	—	—	3.5	—	V _{CC}	V	—	—	—	—

Notes: 1. V_{CC} = 12V

2. V_{CC} = 6.5V

3. For inputting signal to one side channel

HA12229F

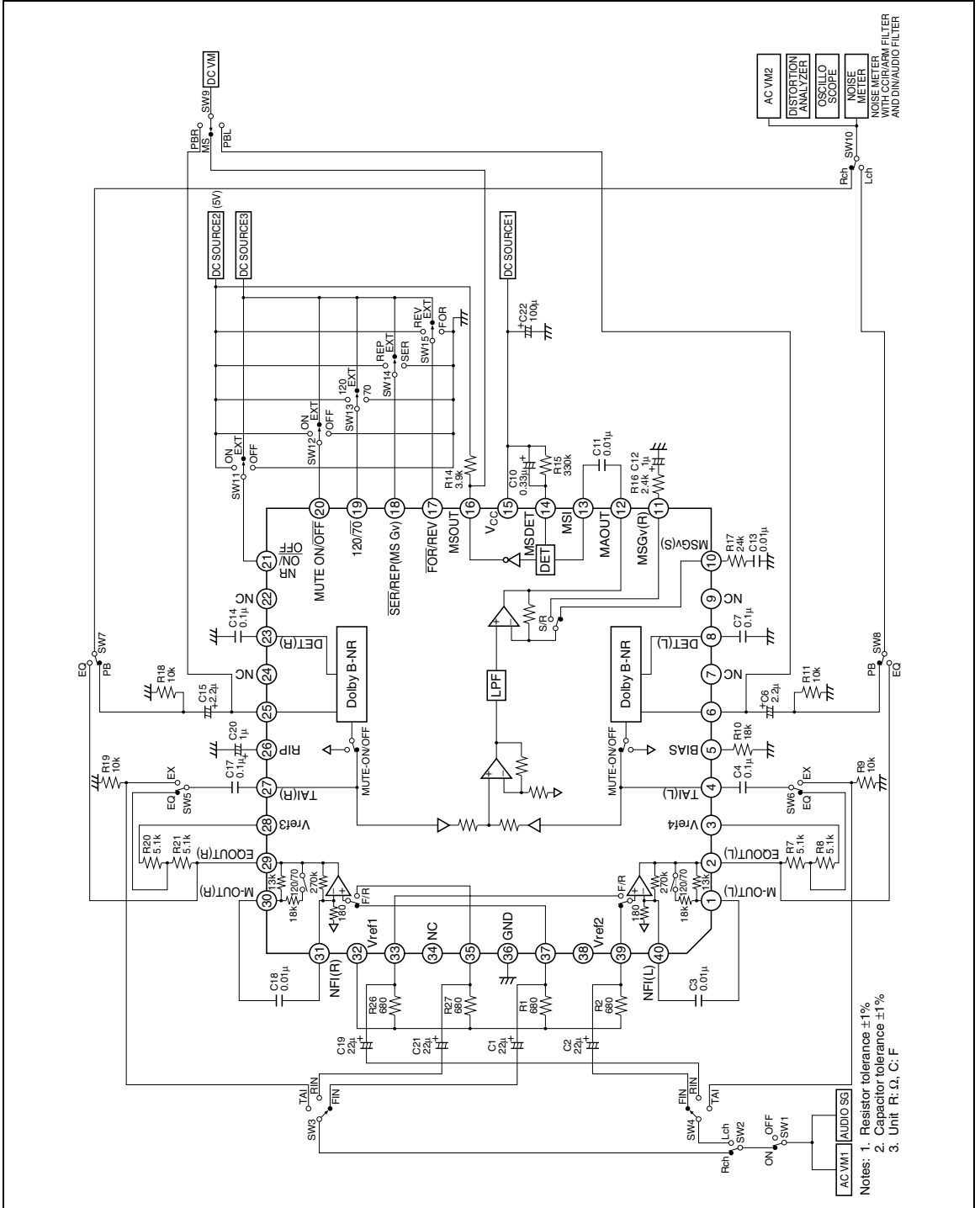
(Ta = 25°C, V_{CC} = 9 V, P_{BOU}T level 0 dB = 300 mVrms, EQOUT level 0 dB = 60 mVrms)

Item	Symbol	Test Condition										Specification				Application Terminal				
		IC Condition					f _{in} (Hz)	P _{BOU} T level (dB)	EQOUT level (dB)	Other	Min	Typ	Max	Unit	Input		Output		COM	Remark
		MUTE ON/OFF	SER/ REP	FOR/ REV	FOR	FOR									R	L	R	L		
Quiescent current	I _q	OFF	70μ	SER	FOR	—	—	—	No signal	3.0	5.0	8.0	mA	—	—	—	—	—	15	
Input Amp. gain	G _{vIA}	OFF	—	—	—	1k	0	—	No signal	19.0	20.0	21.0	dB	27	4	25	6	—	—	
P _{BOU} T offset	V _{ofs}	OFF→ ON	—	—	—	—	—	—	No signal	-150	0	150	mV	—	—	25	6	—	—	1
Signal handling	V _{o max}	OFF	—	—	—	1k	—	—	THD=1%	12.0	13.0	—	dB	27	4	25	6	—	—	2
Signal to noise ratio	S/N	OFF	—	—	—	1k	(0)	—	Rg=10kΩ, CCIR/ARM	70.0	80.0	—	dB	27	4	25	6	—	—	
Total Harmonic Distortion	THD	OFF	—	—	—	1k	0	—	—	—	0.05	0.3	%	27	4	25	6	—	—	
Channel separation	CTRL (1)	—	—	—	FOR	1k	(+20)	—	—	50.0	60.0	—	dB	37	39	29	2	2	2	29
	CTRL (2)	OFF	—	—	—	1k	(+12)	—	—	70.0	80.0	—	dB	27	4	25	6	25	6	25
MUTE attenuation	CT MUTE	OFF→ ON	—	—	—	1k	(+12)	—	—	70.0	80.0	—	dB	27	4	25	6	—	—	
PB-EQ gain	G _v EQ 1k	—	120μ	—	FOR/ REV	1k	—	0	—	37.8	40.8	43.8	dB	37/35	39/33	29	2	—	—	
	G _v EQ 10k(1)	—	120μ	—	FOR	10k	—	0	—	33.9	36.9	39.9	dB	37	39	29	2	—	—	
	G _v EQ 10k(2)	—	70μ	—	FOR	10k	—	0	—	29.6	32.6	35.6	dB	37	39	29	2	—	—	
PB-EQ Maximum output level	V _{OM}	—	120μ	—	FOR	1k	—	—	THD=1%	300	600	—	mVrms	37	39	29	2	—	—	
PB-EQ T.H.D.	THD-EQ	—	120μ	—	FOR/ REV	1k	—	+14dB	—	—	0.1	0.3	%	37/35	39/33	29	2	—	—	
PB-EQ input conversion noise	V _N	—	120μ	—	FOR/ REV	(1k)	—	—	Rg=680Ω, DIN-AUDIO	—	0.7	1.5	μVrms	37/35	39/33	29	2	—	—	
MS sensing level	V _{ON} (1)	OFF	—	SER	—	5k	—	—	—	-36.0	-32.0	-28.0	dB	27	4	25	6	16	3	
	V _{ON} (2)	OFF	—	REP	—	5k	—	—	—	-18.0	-14.0	-10.0	dB	27	4	25	6	16	3	
MS output low level	V _{OL}	OFF	—	SER	—	5k	0	—	—	—	1.0	1.5	V	27	4	—	—	—	—	16
MS output leakage current	I _{OH}	—	—	—	—	—	—	—	No signal	—	0.0	2.0	μA	—	—	—	—	—	—	16
Control voltage	V _{IL}	—	—	—	—	—	—	—	—	-0.2	—	1.0	V	—	—	—	—	—	—	17 to
	V _{IH}	—	—	—	—	—	—	—	—	3.5	—	V _{CC}	V	—	—	—	—	—	—	20

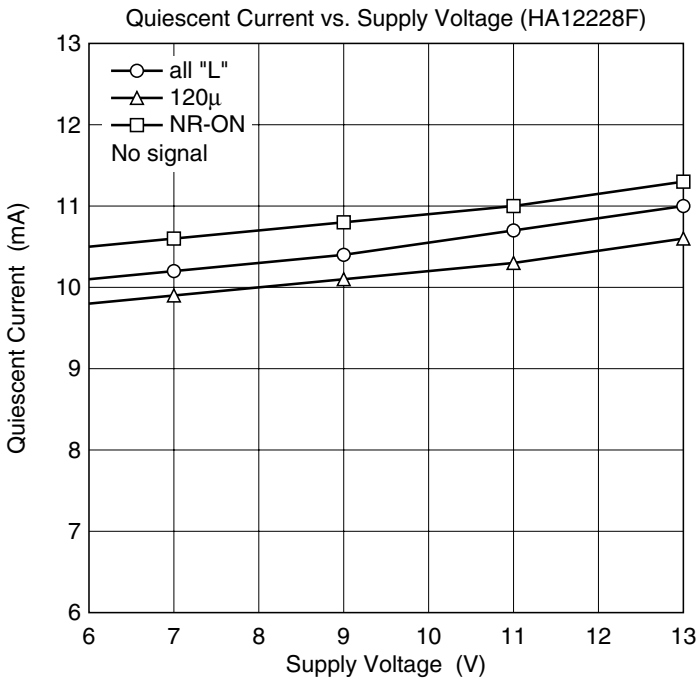
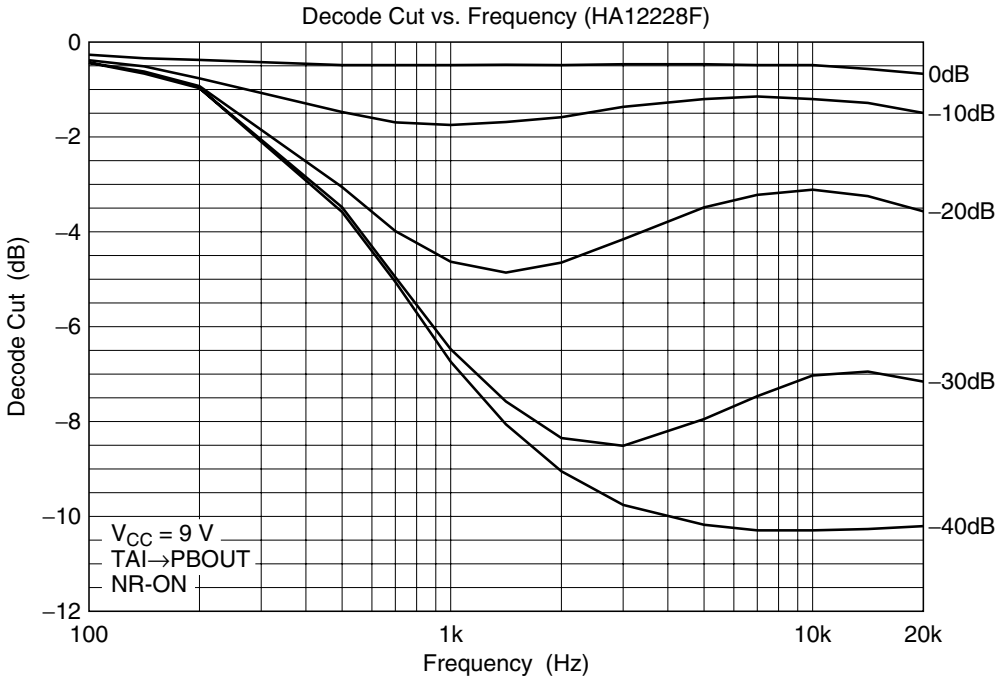
Notes: 1. V_{CC} = 12V
 2. V_{CC} = 6.5V
 3. For inputting signal to one side channel

HA12228F/HA12229F

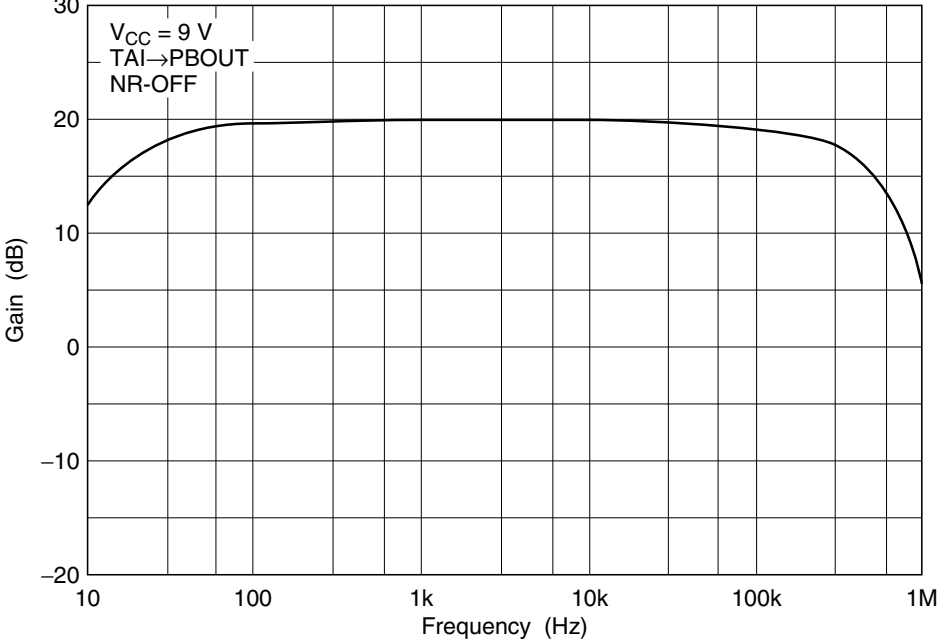
Test Circuit



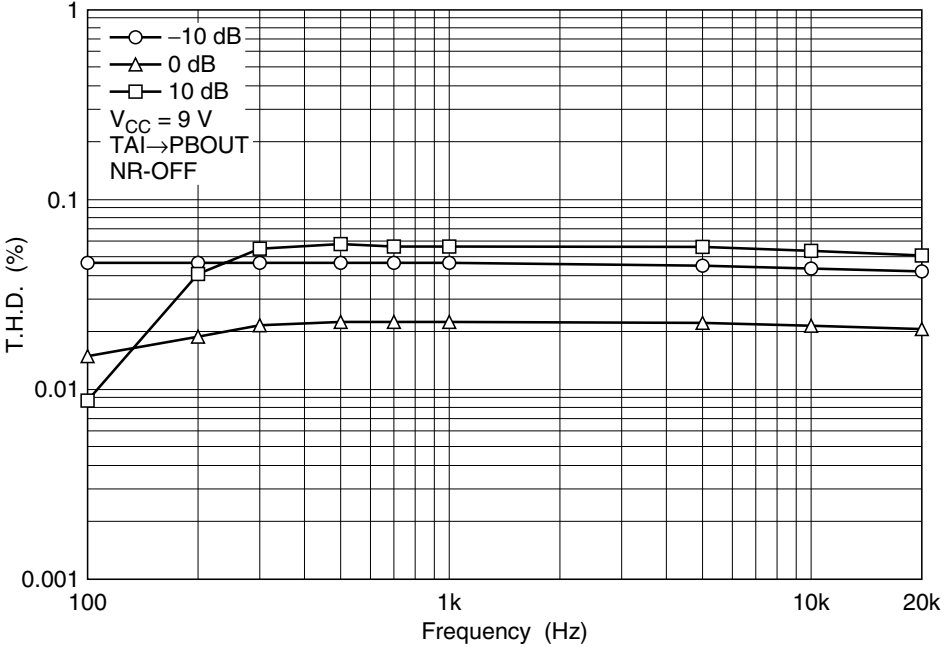
Characteristic Curves

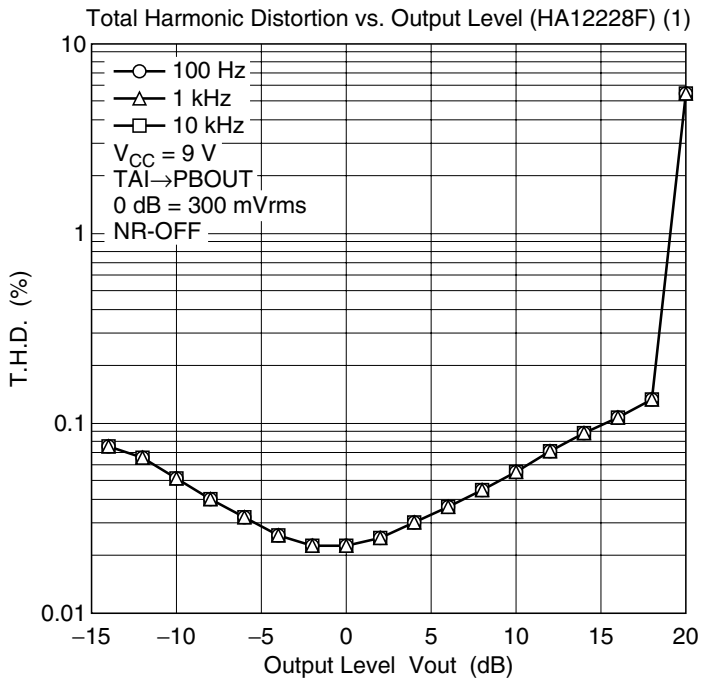
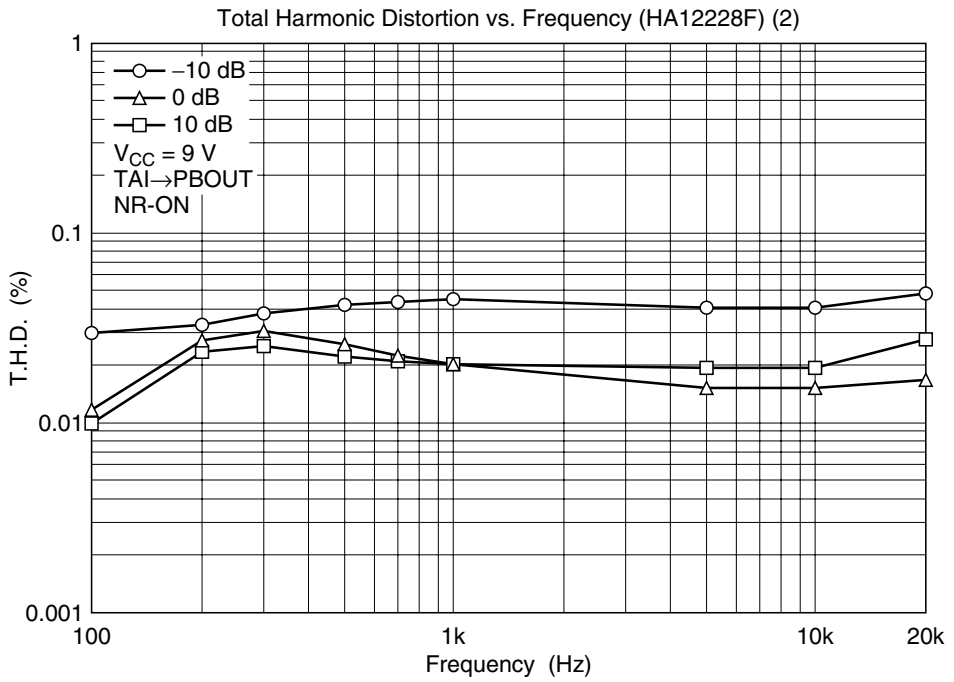


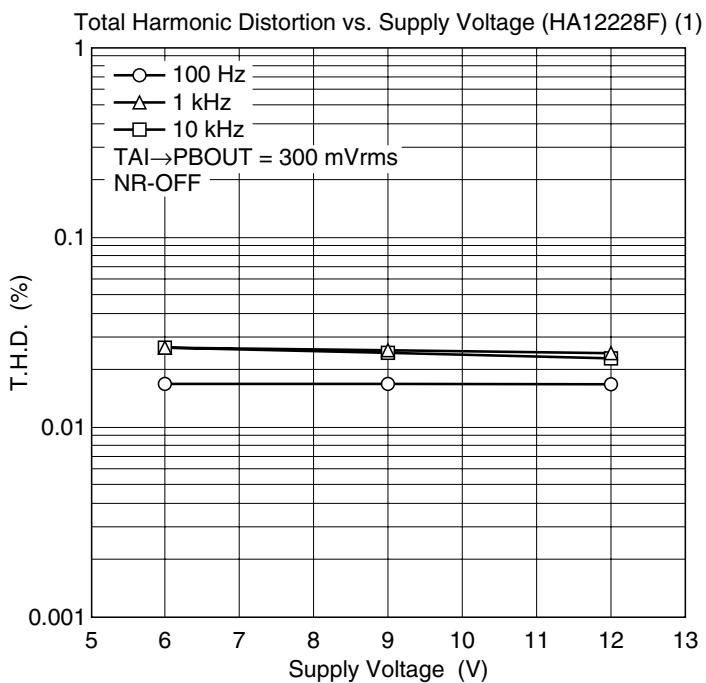
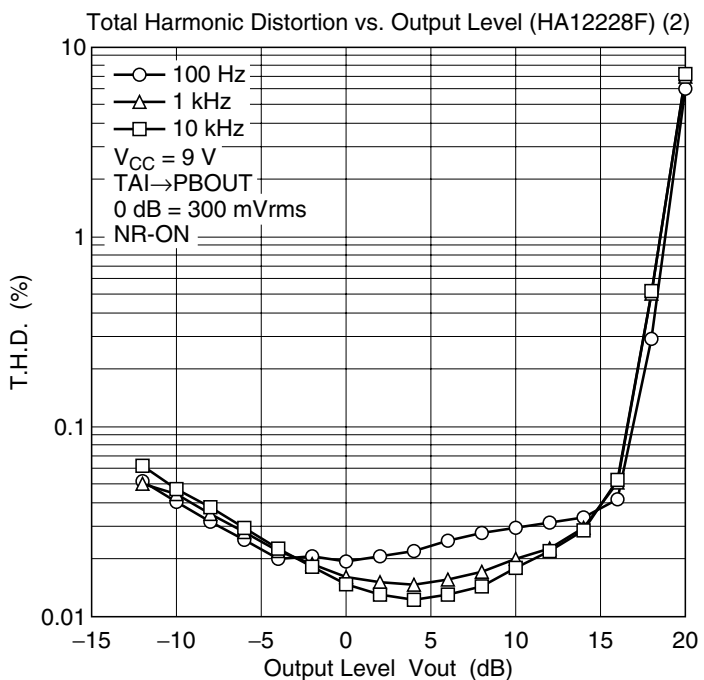
Input Amp. Gain vs. Frequency (HA12228F)

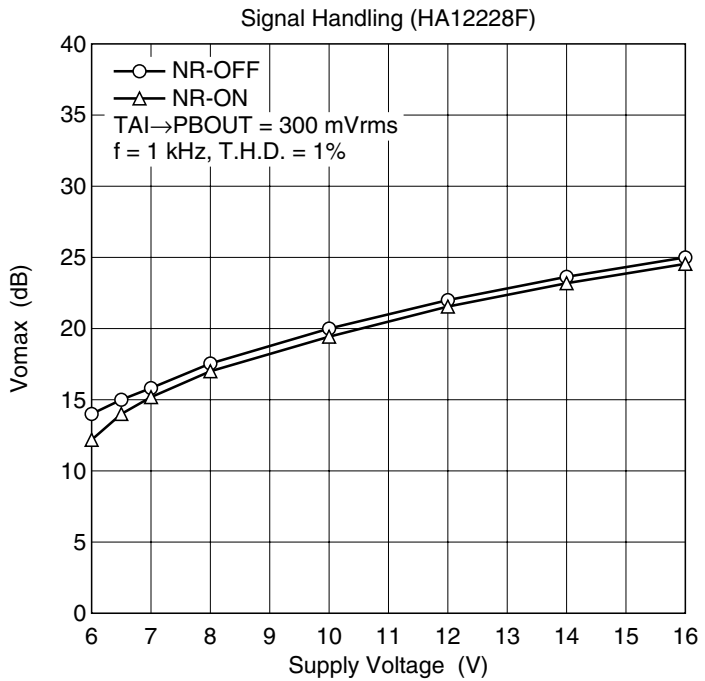
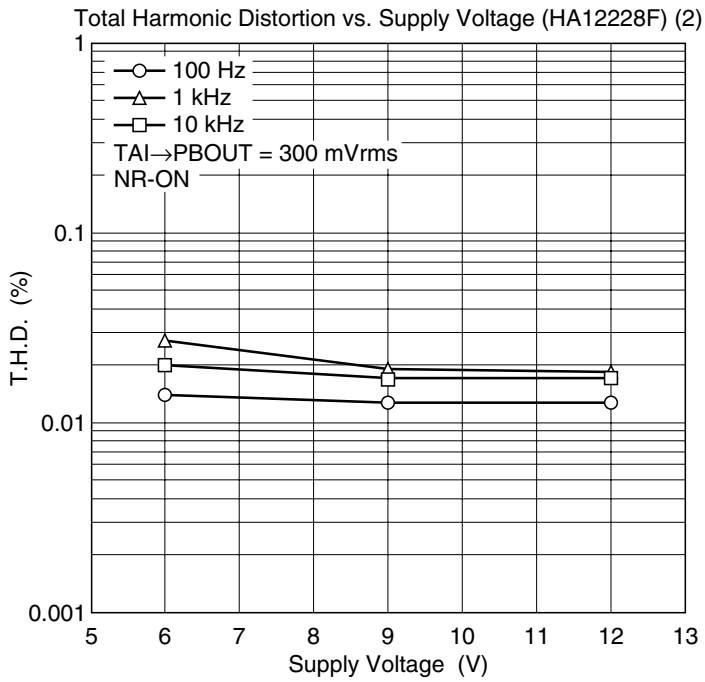


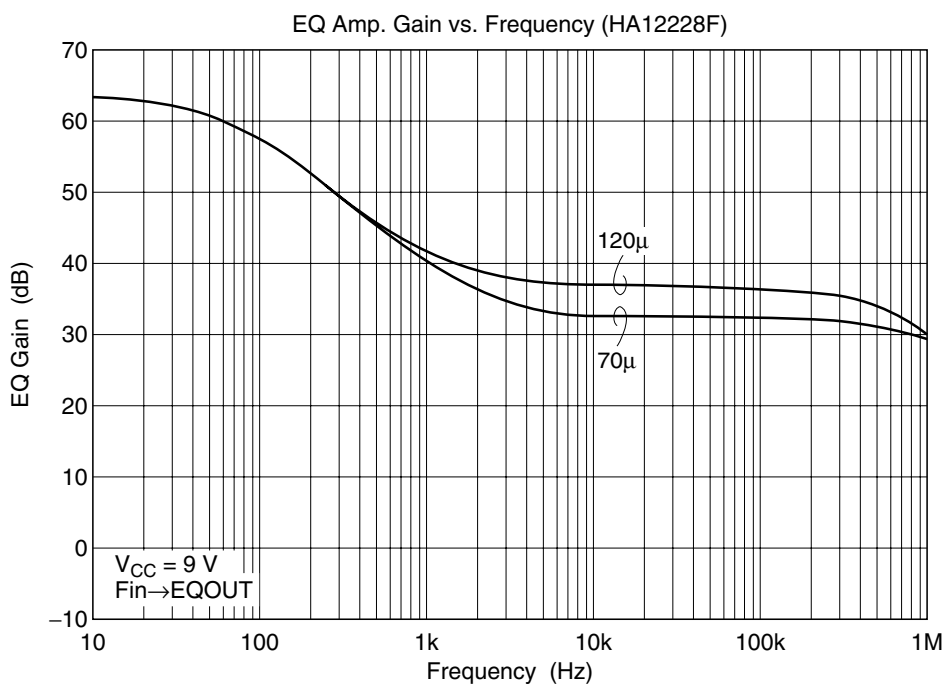
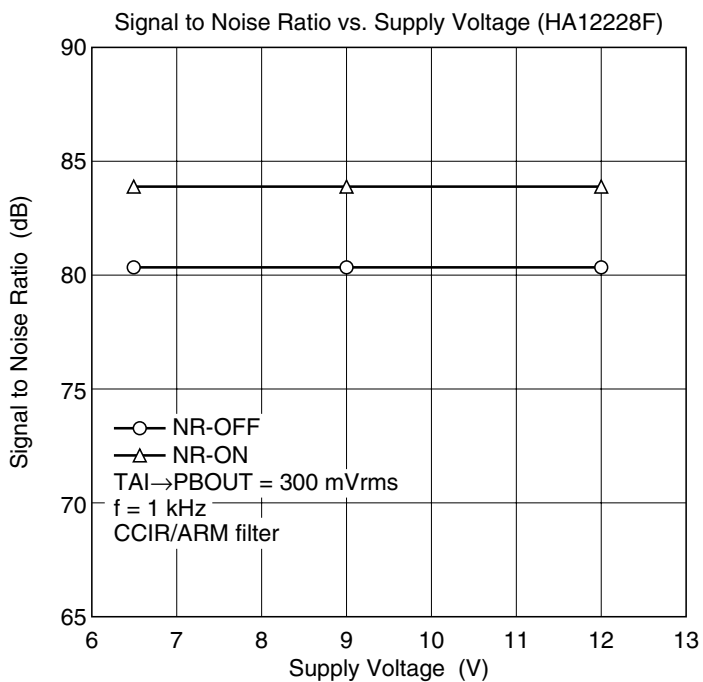
Total Harmonic Distortion vs. Frequency (HA12228F) (1)

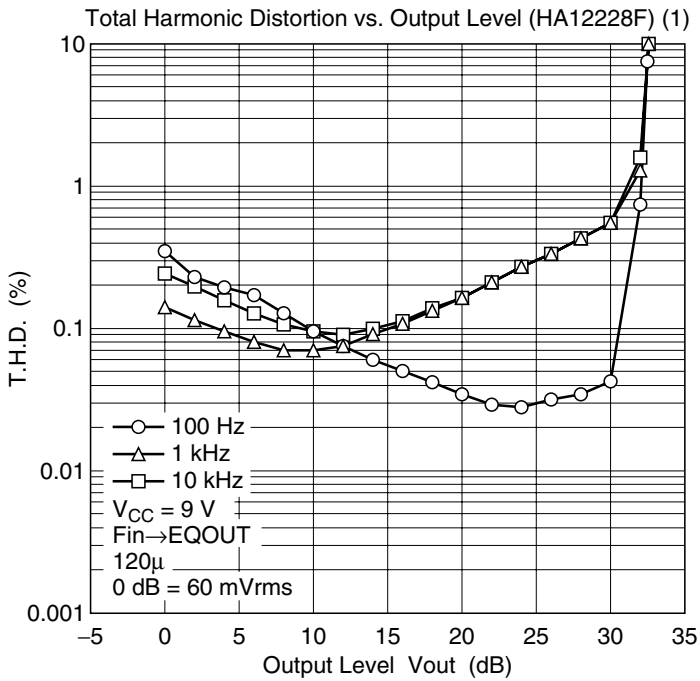
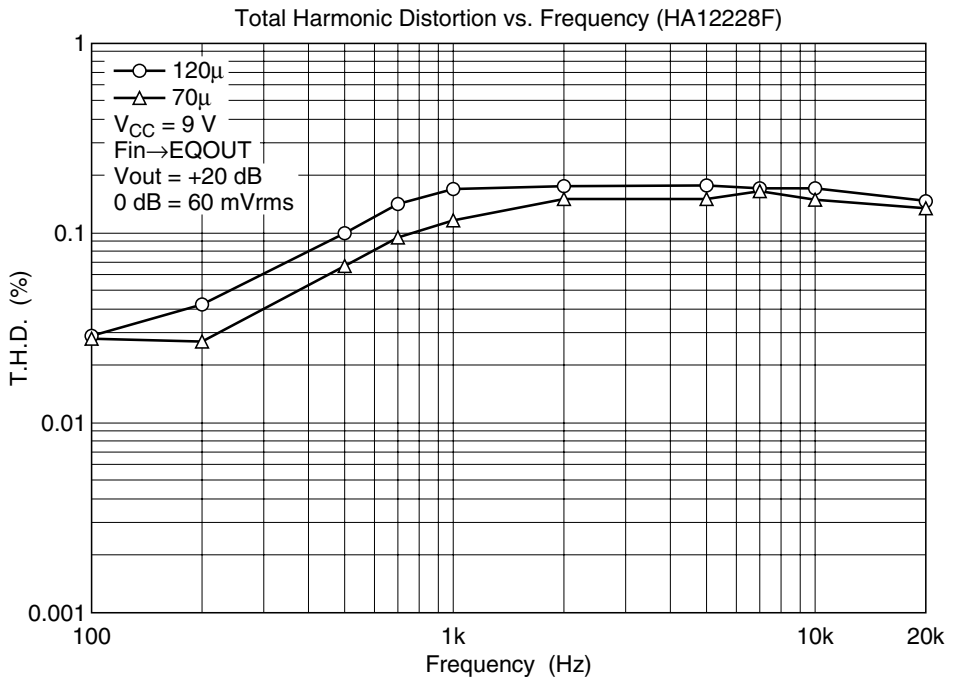


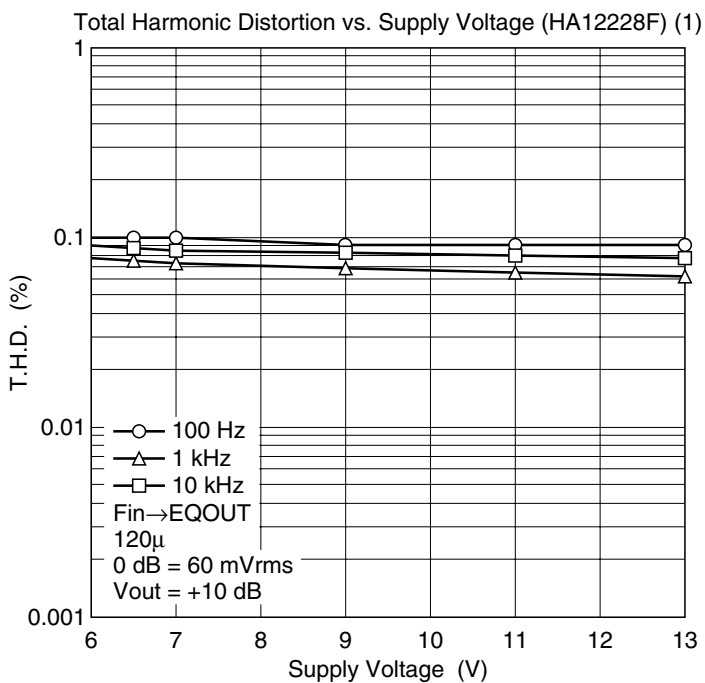
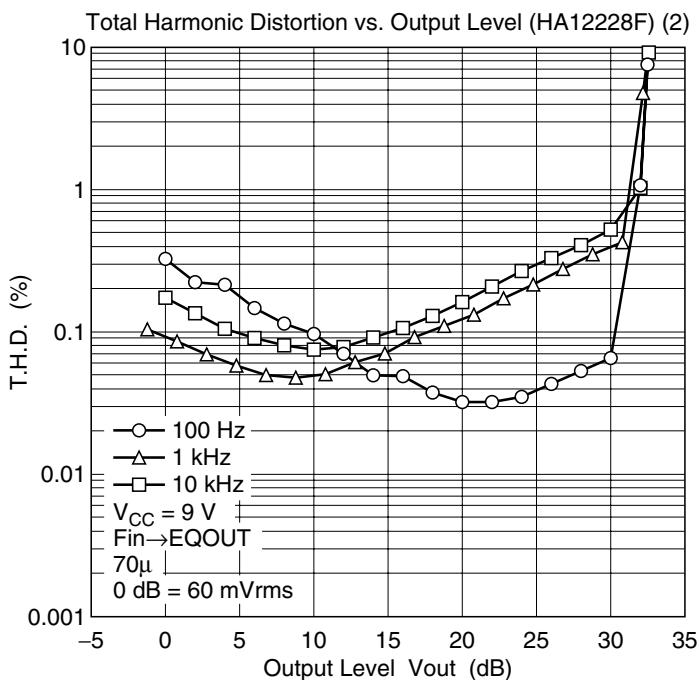


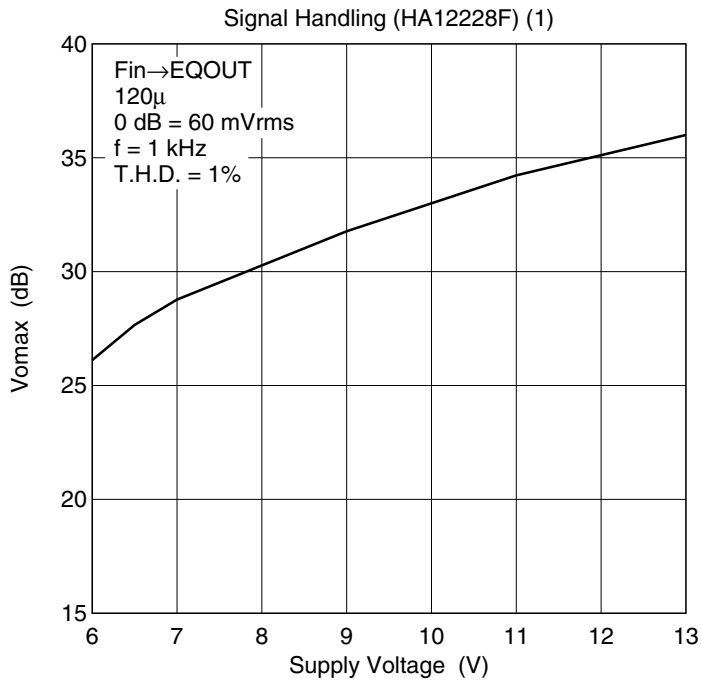
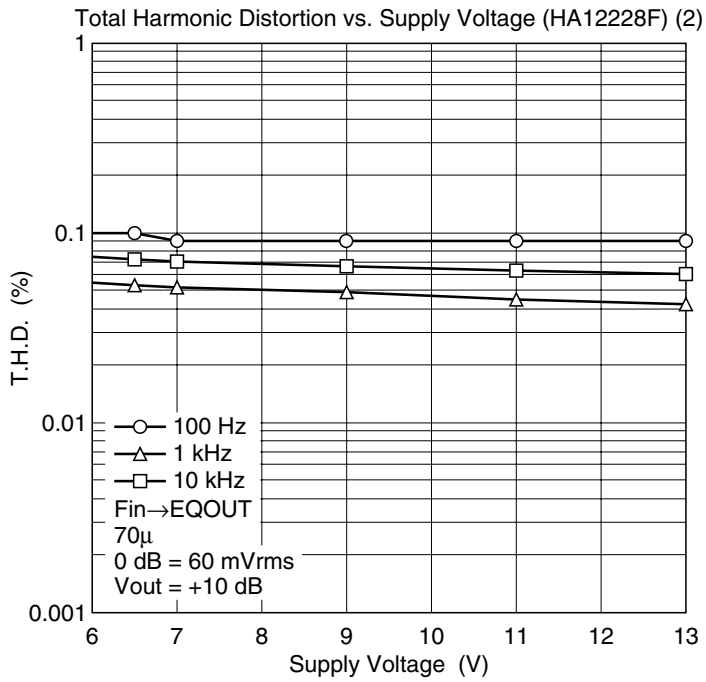


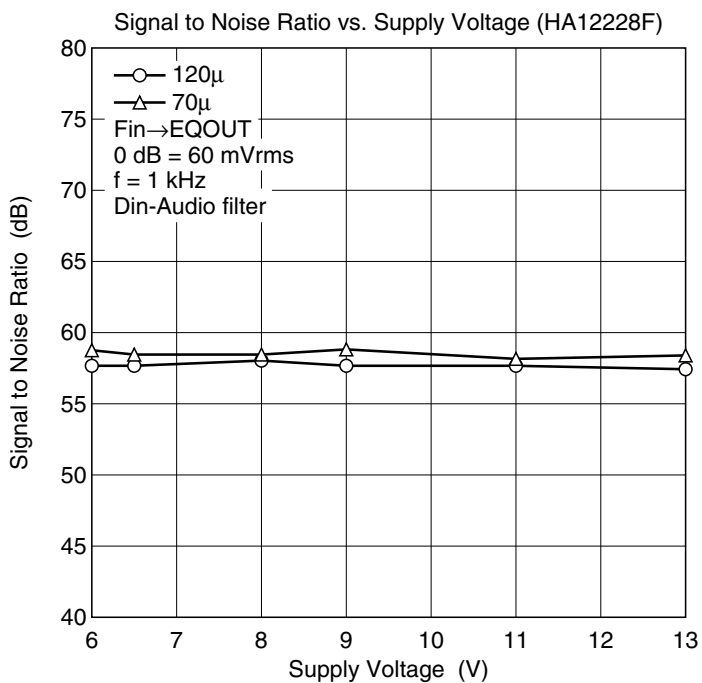
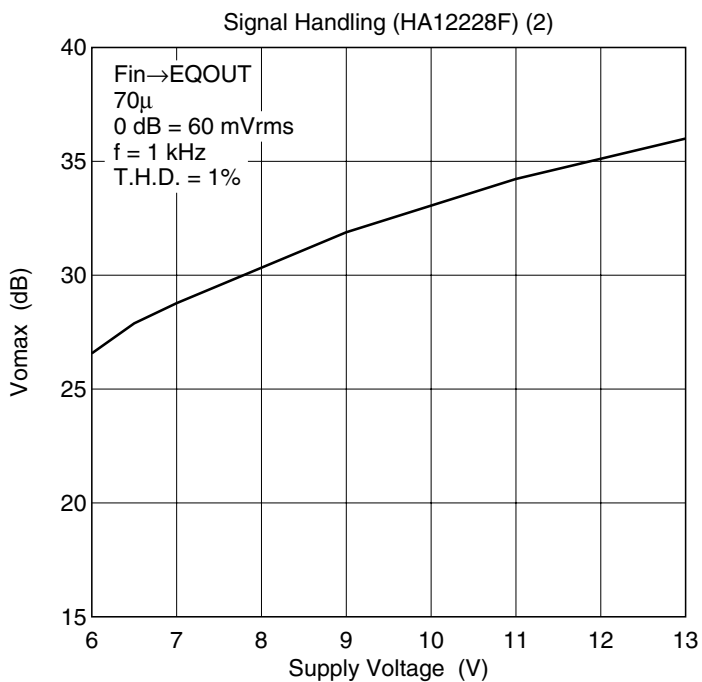




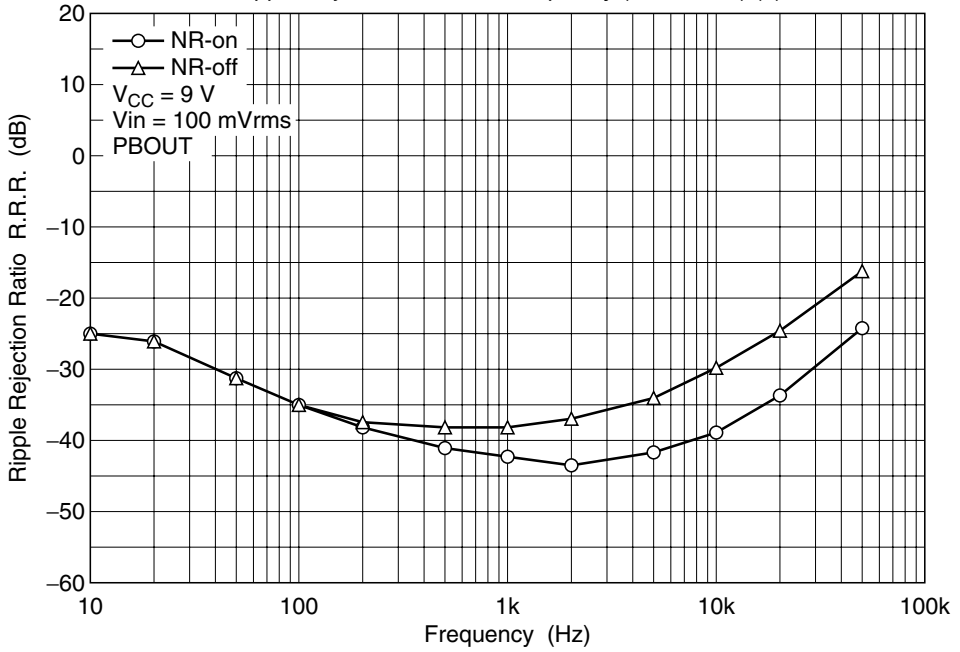




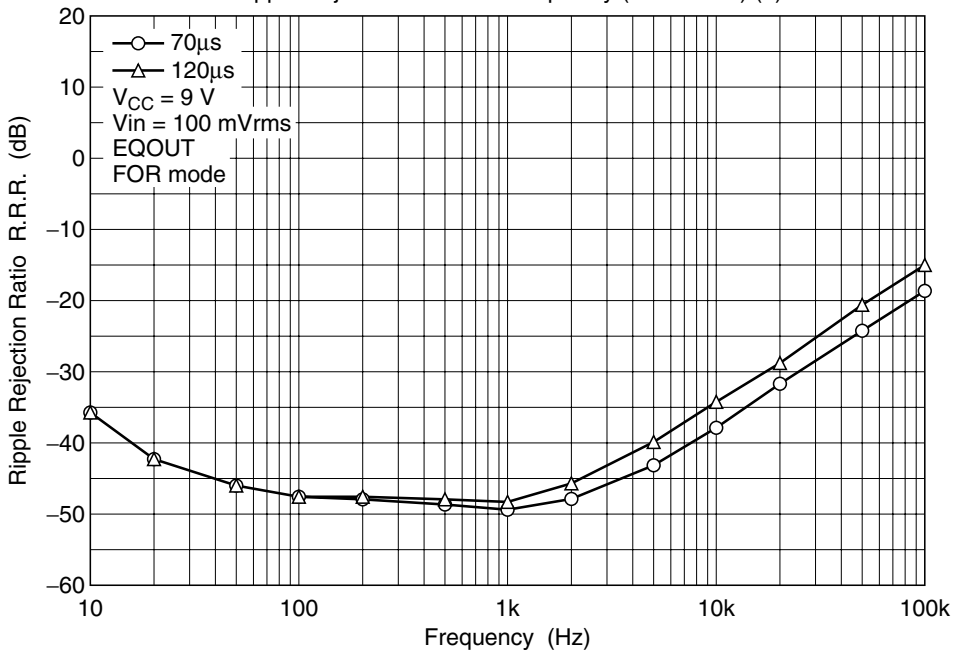




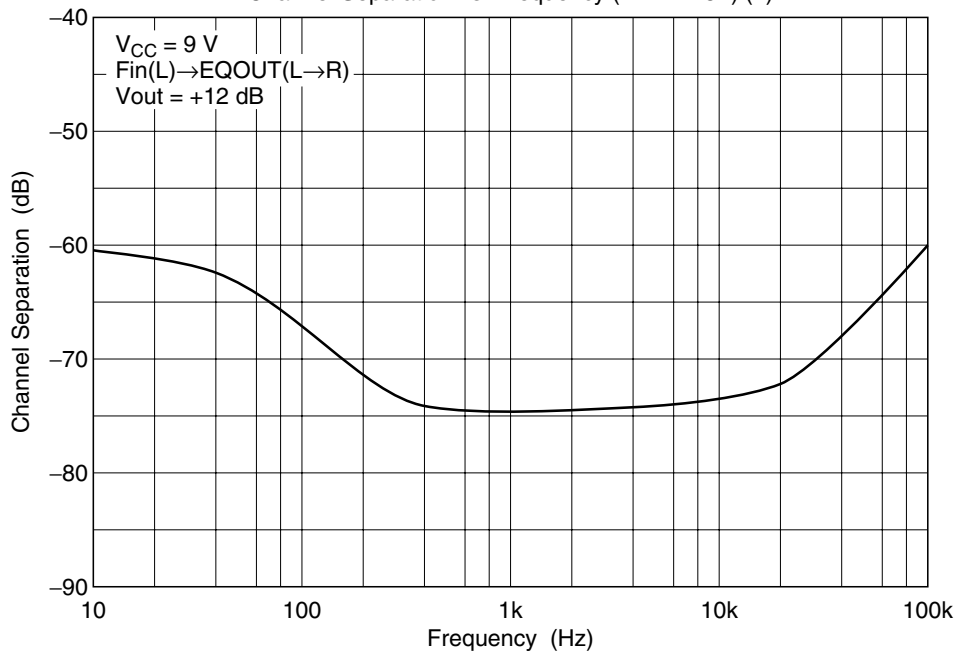
Ripple Rejection Ratio vs. Frequency (HA12228F) (1)



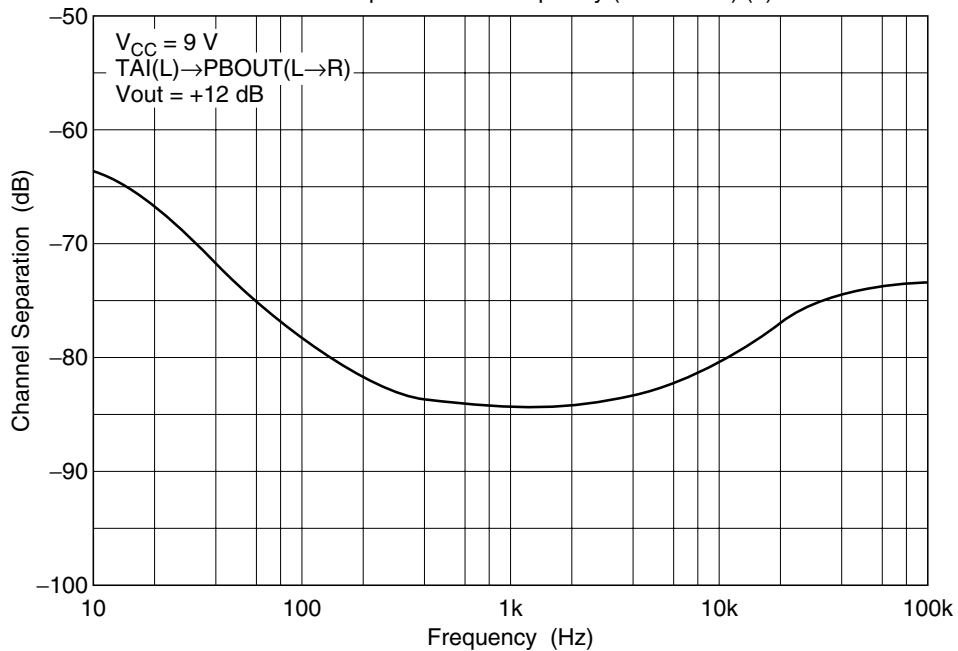
Ripple Rejection Ratio vs. Frequency (HA12228F) (2)

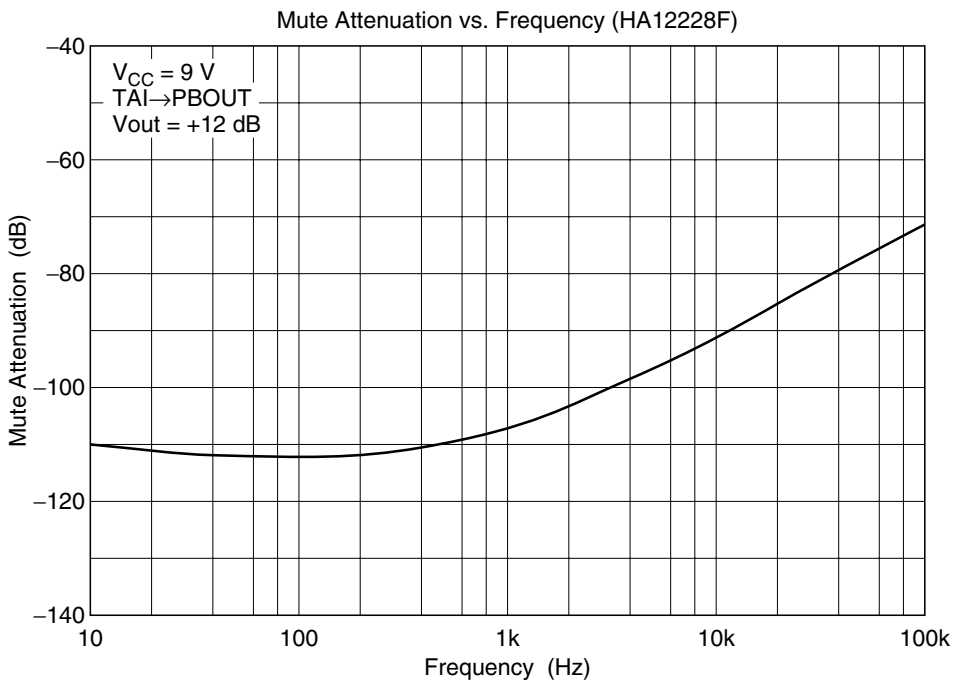
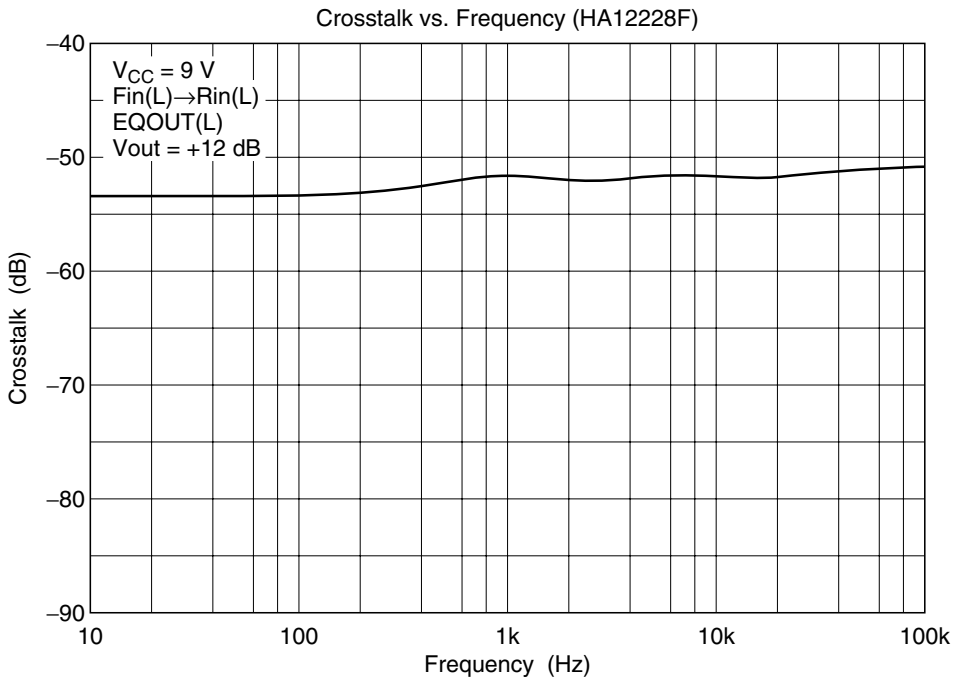


Channel Separation vs. Frequency (HA12228F) (1)

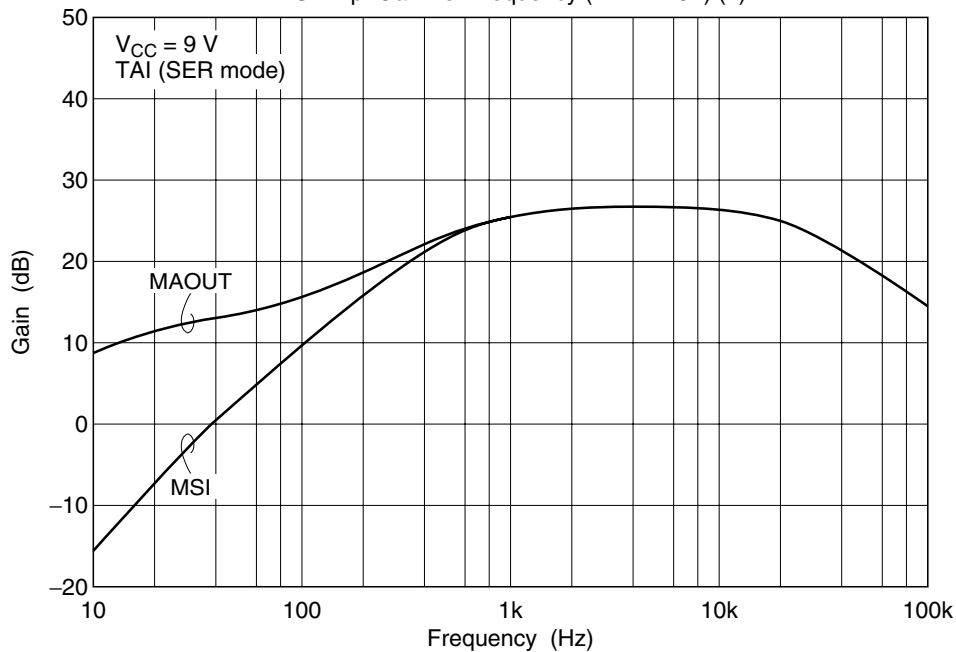


Channel Separation vs. Frequency (HA12228F) (2)

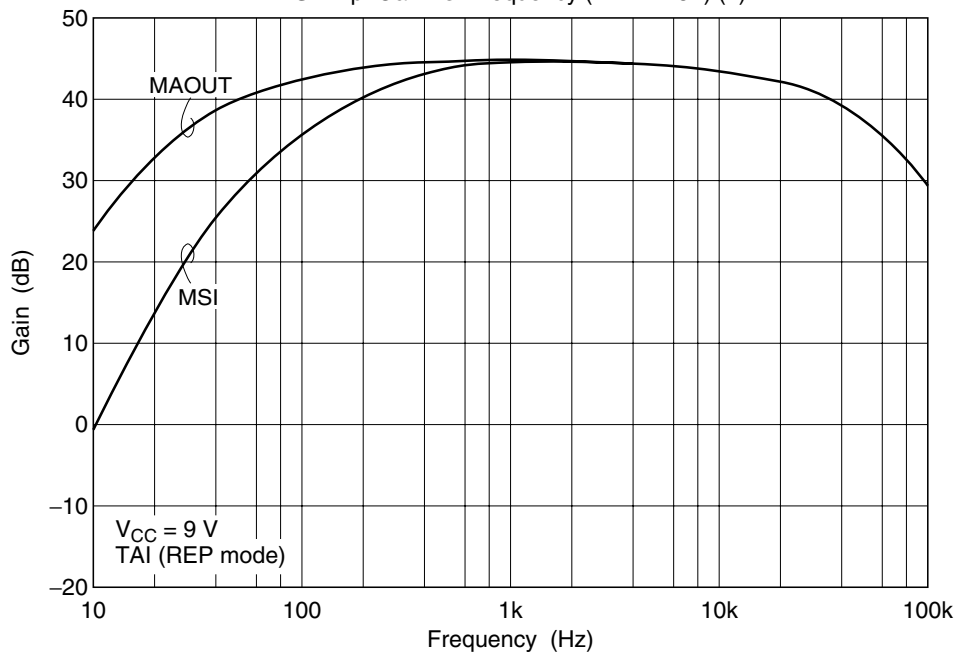


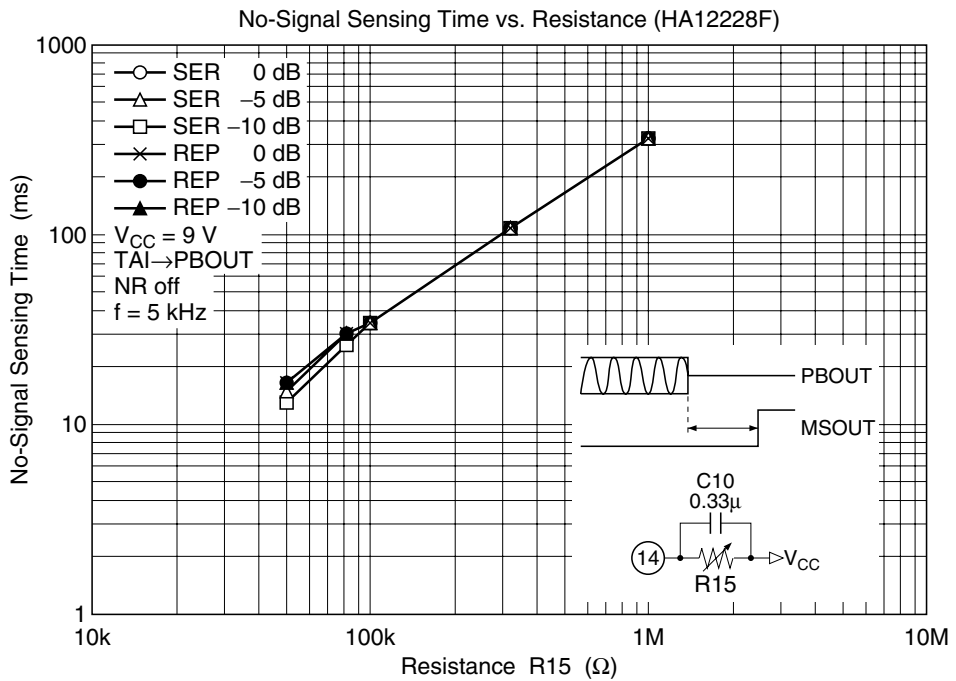
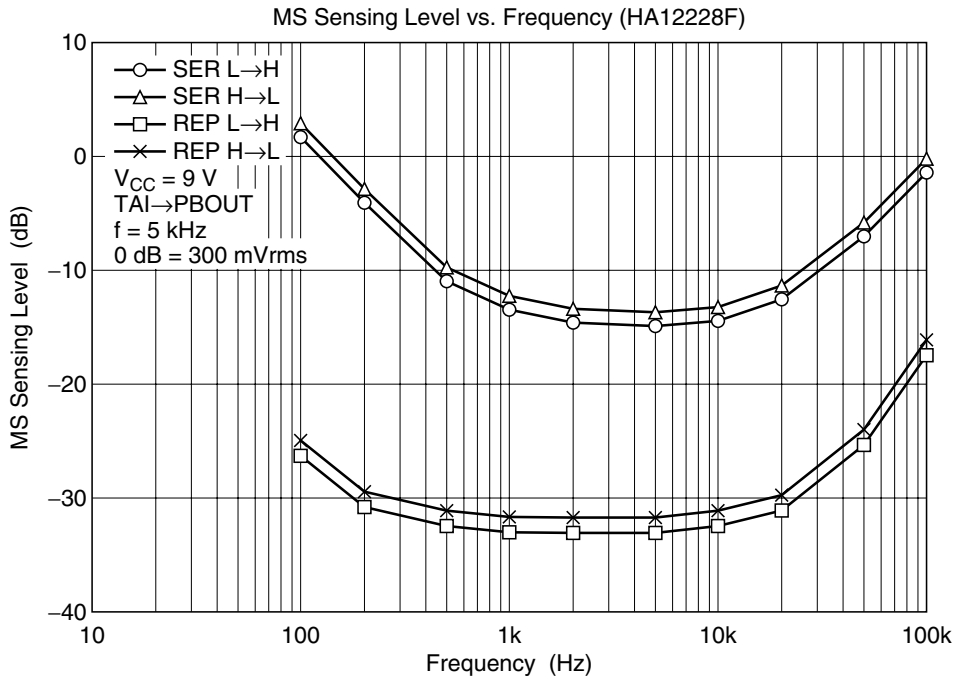


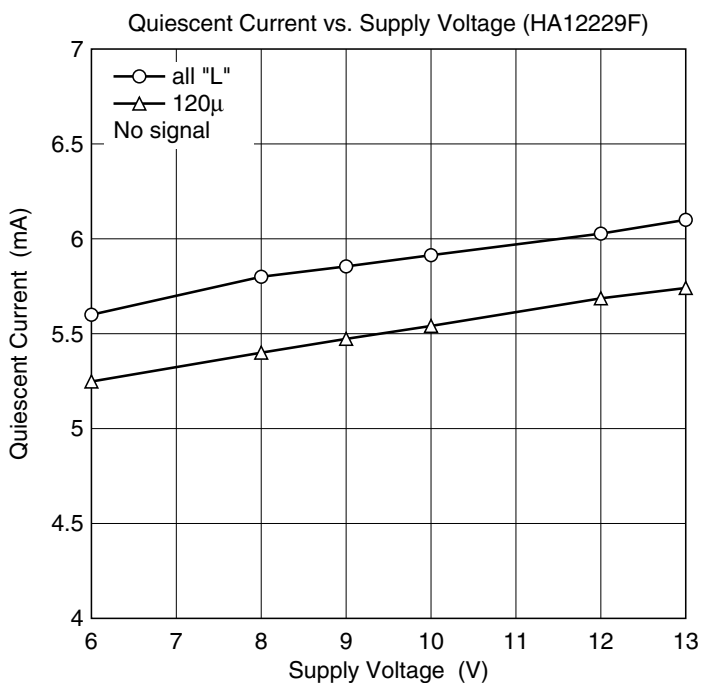
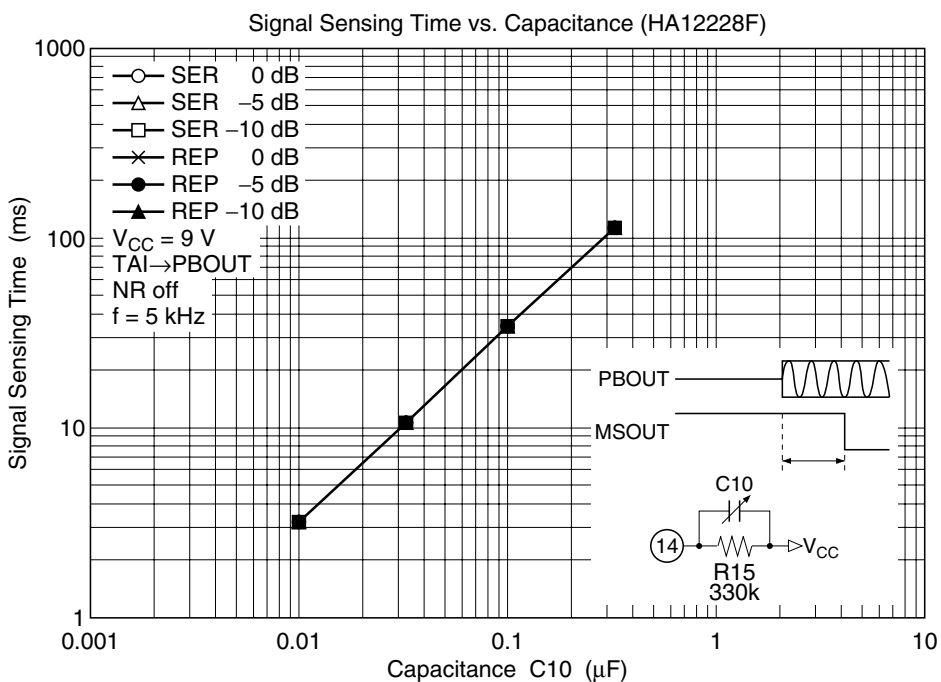
MS Amp. Gain vs. Frequency (HA12228F) (1)



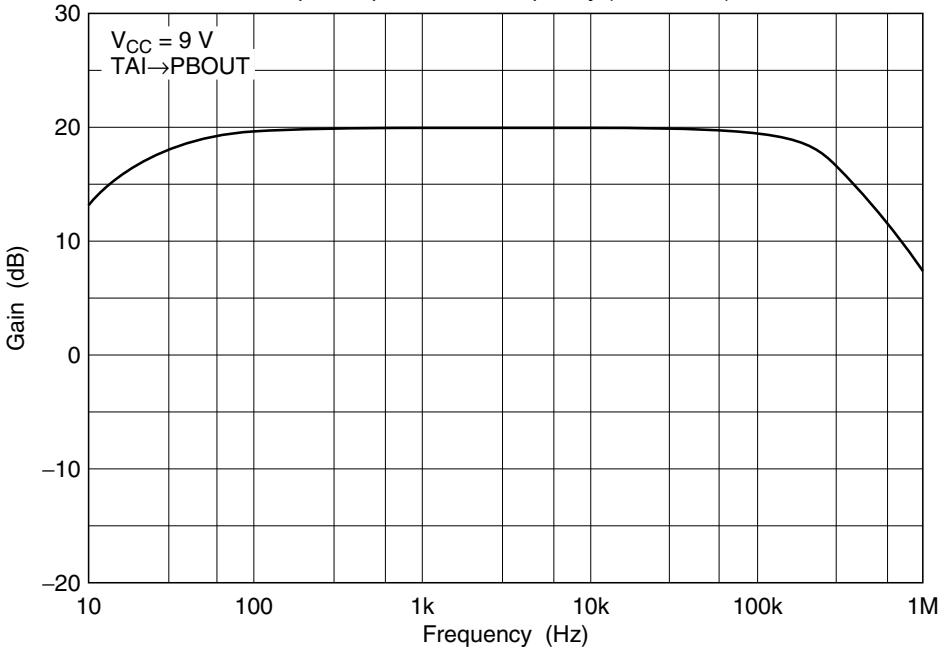
MS Amp. Gain vs. Frequency (HA12228F) (2)



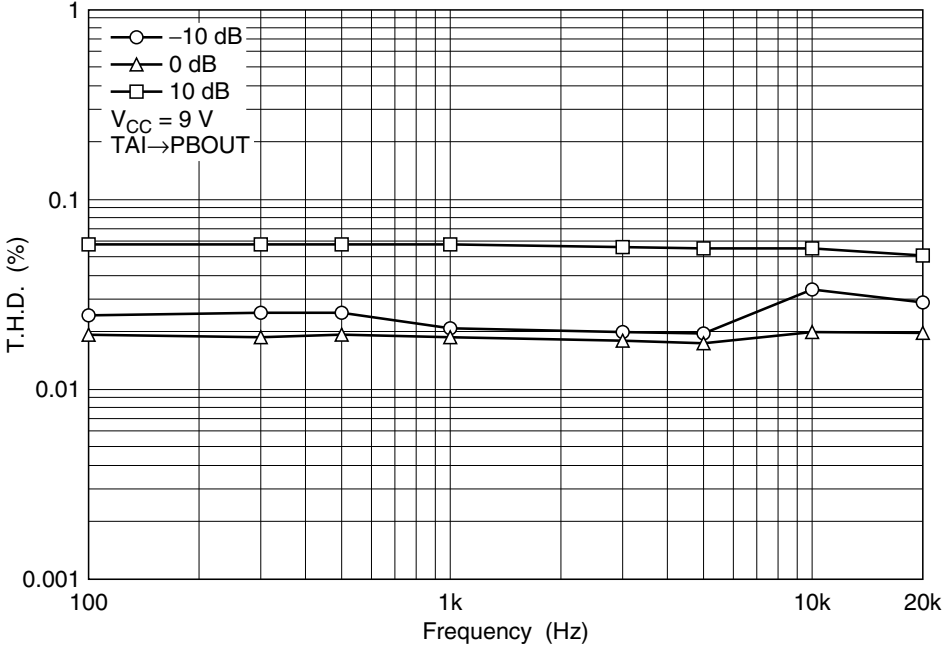


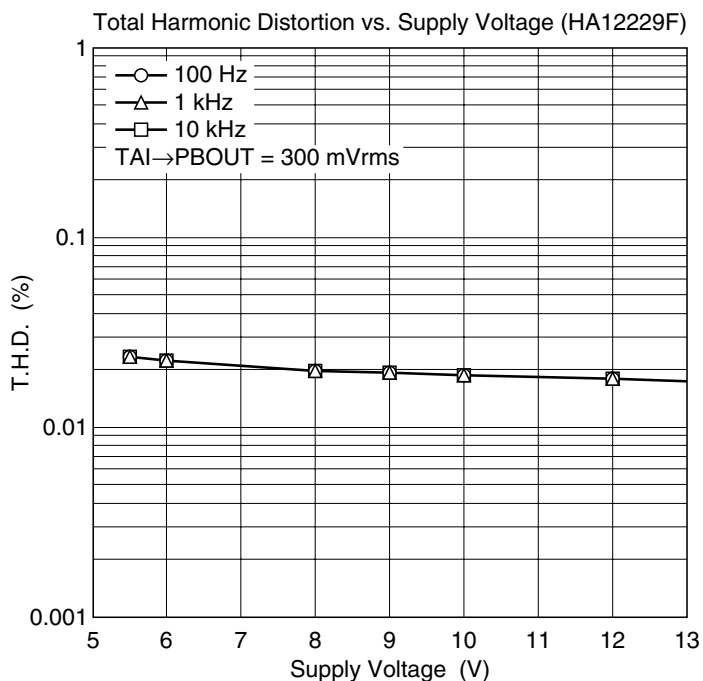
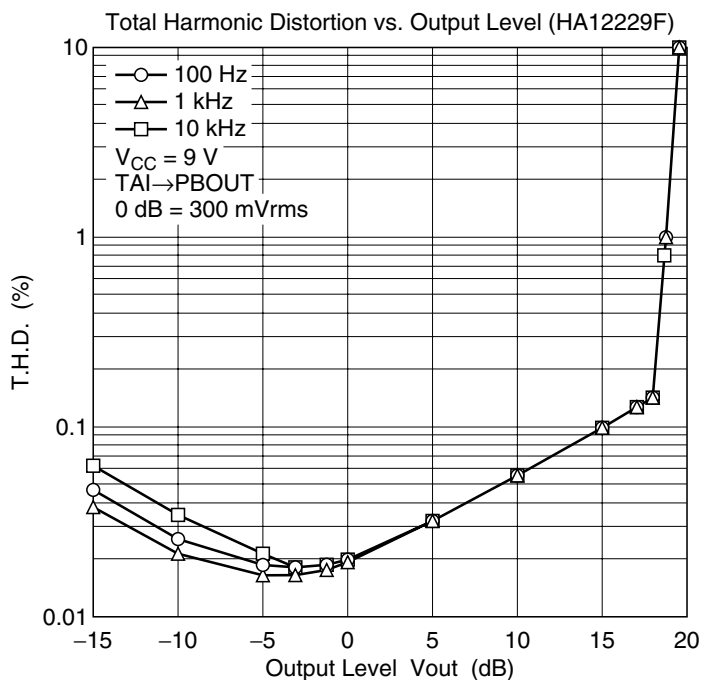


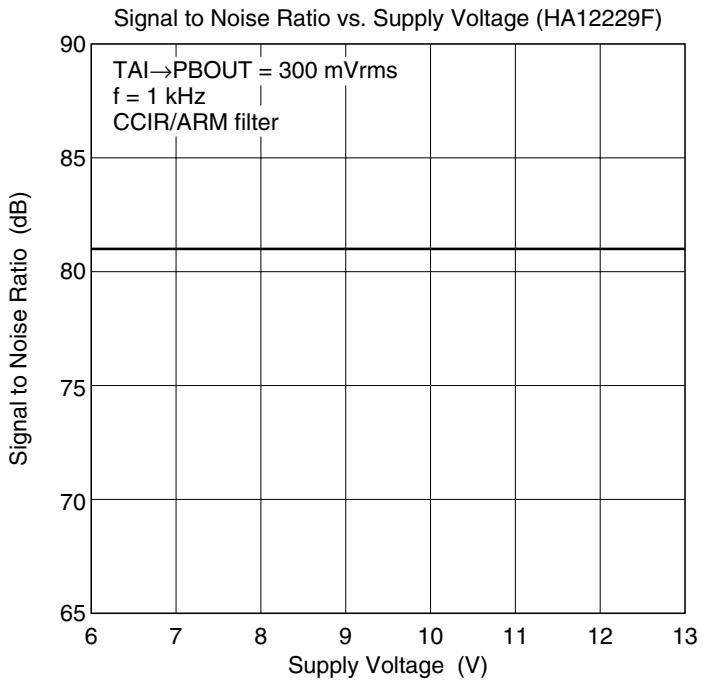
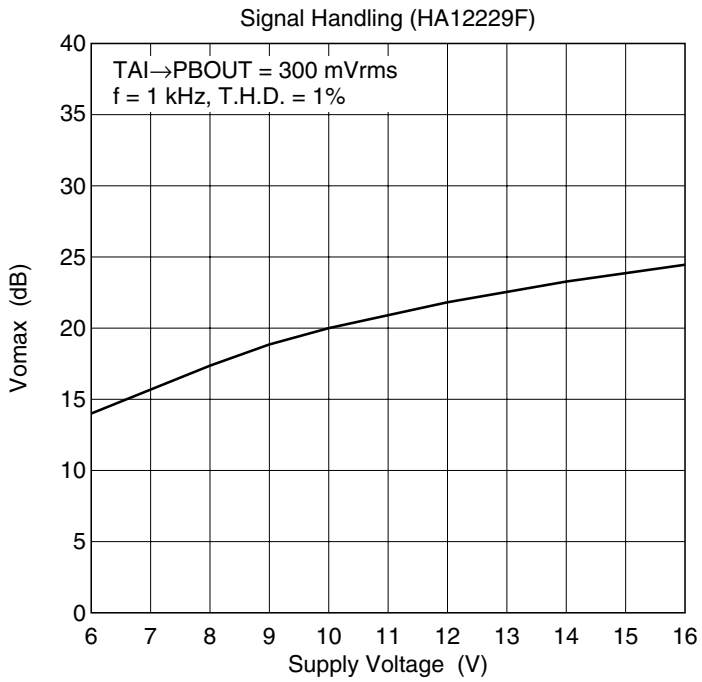
Input Amp. Gain vs. Frequency (HA12229F)



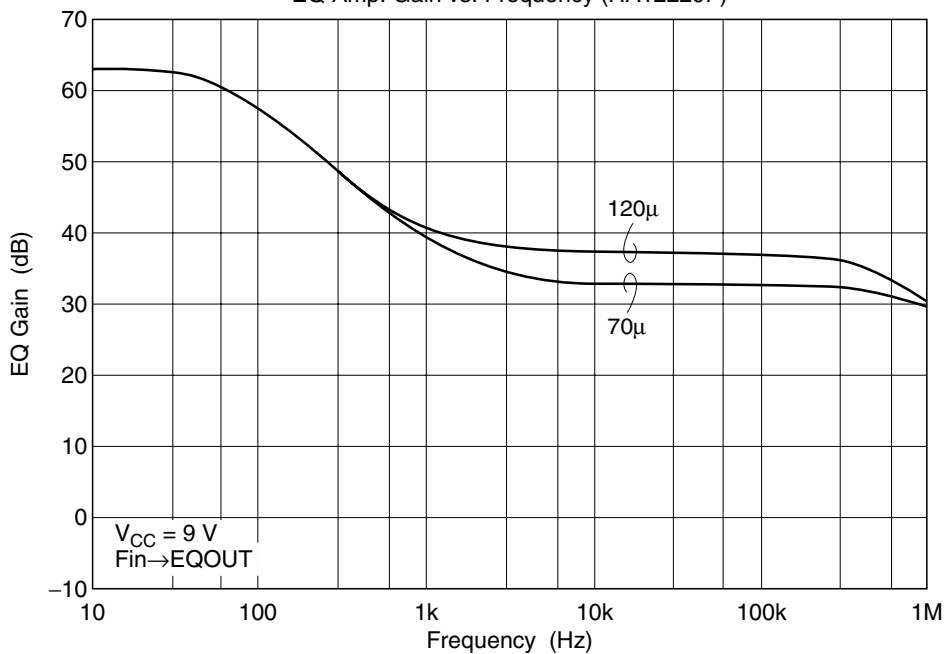
Total Harmonic Distortion vs. Frequency (HA12229F)



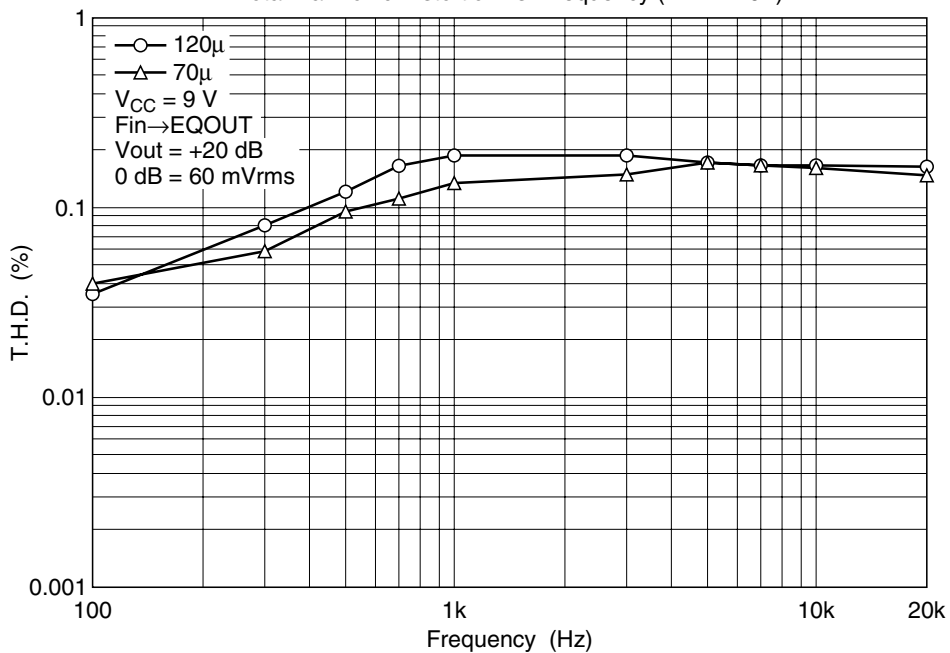


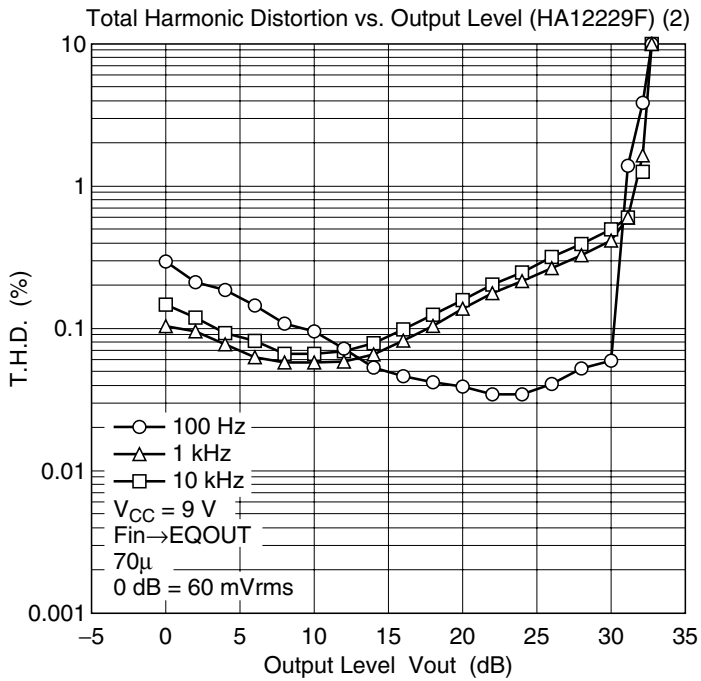
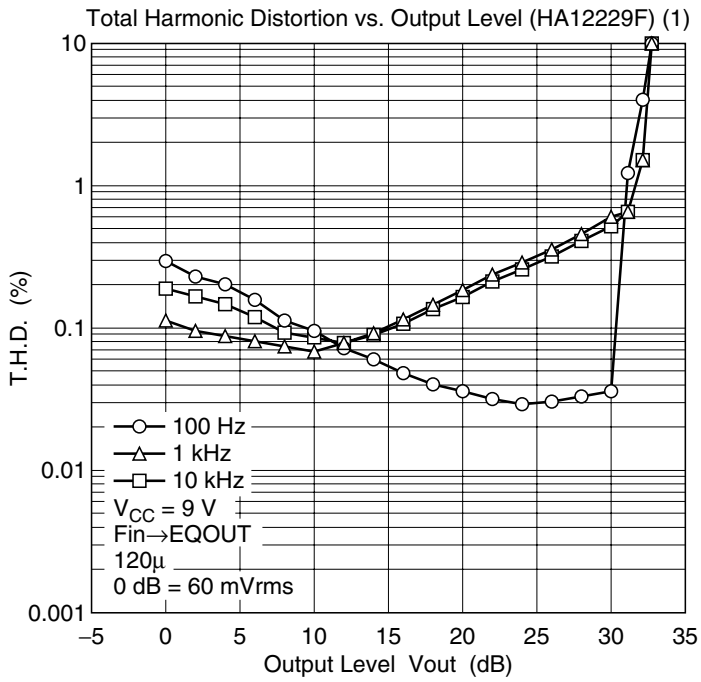


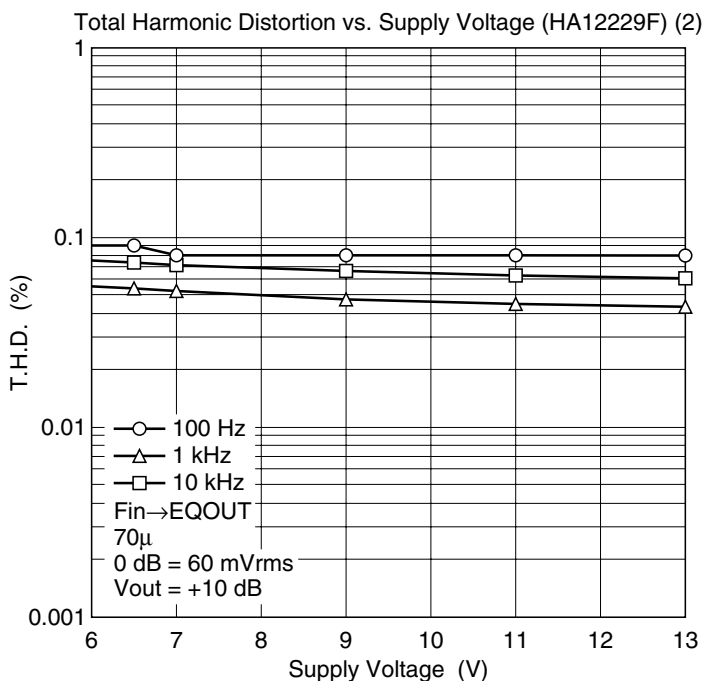
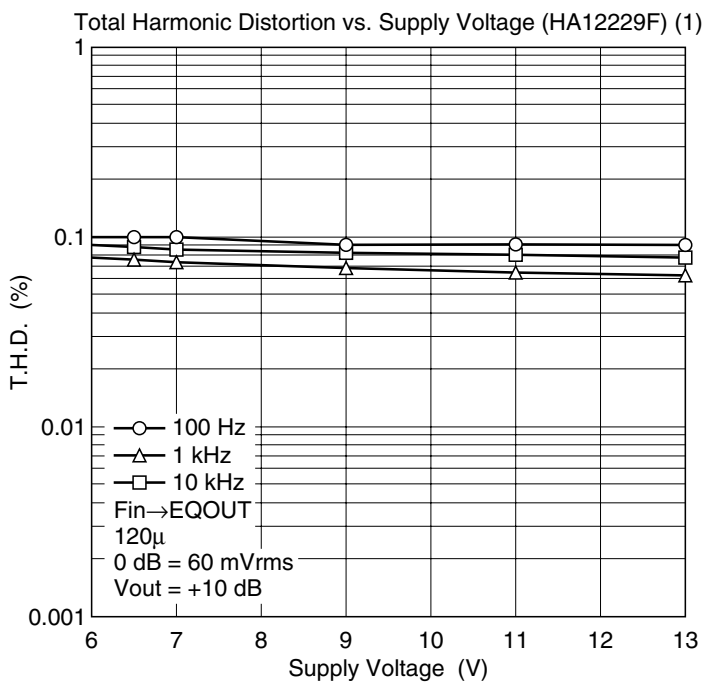
EQ Amp. Gain vs. Frequency (HA12229F)



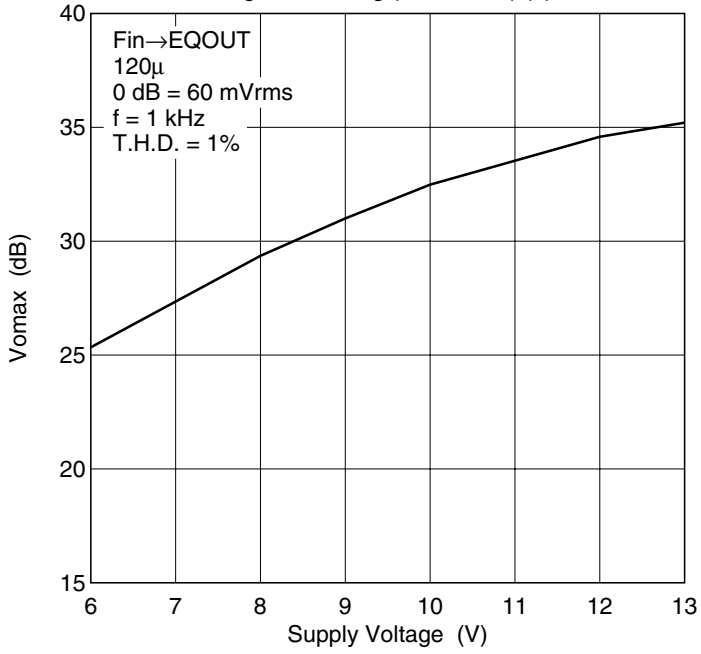
Total Harmonic Distortion vs. Frequency (HA12229F)



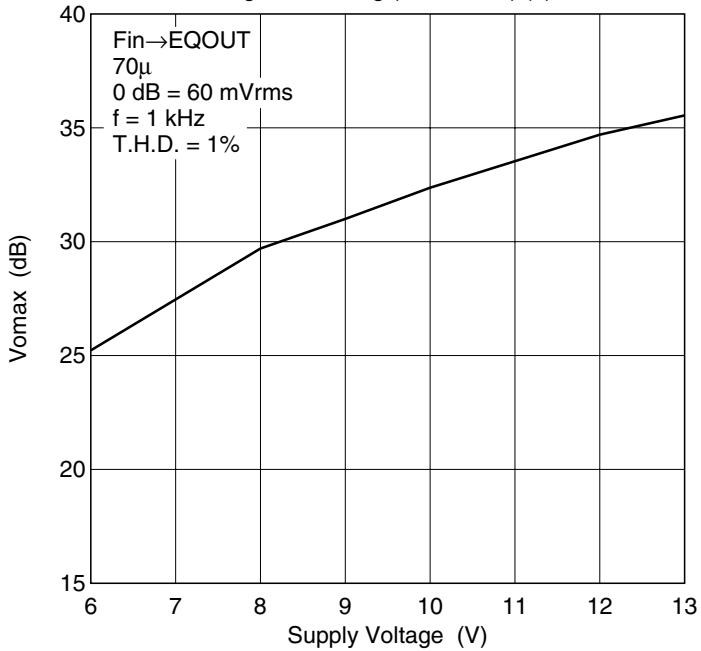


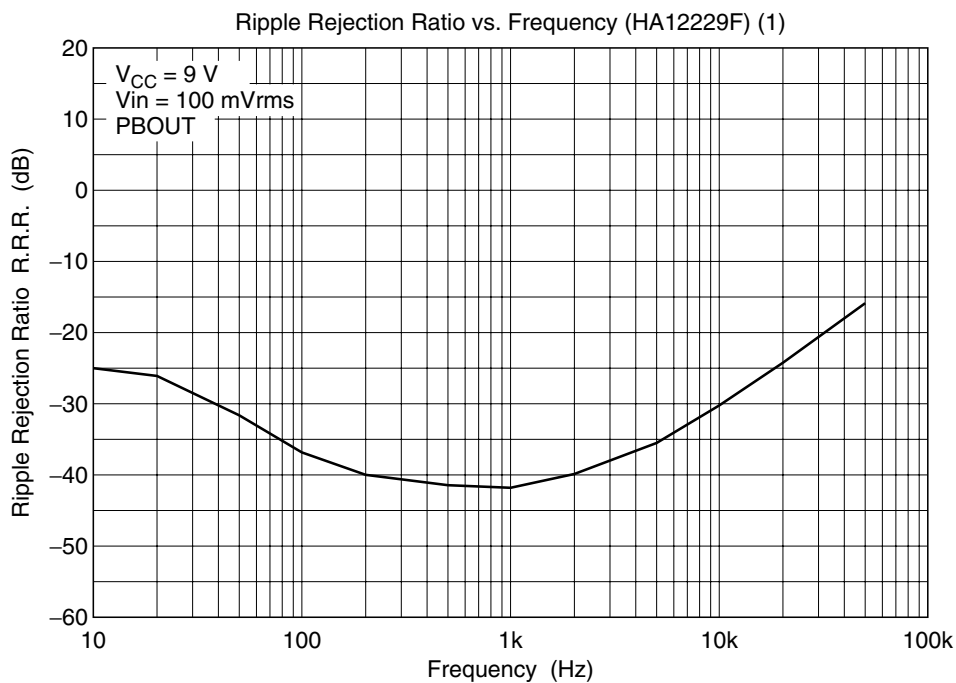
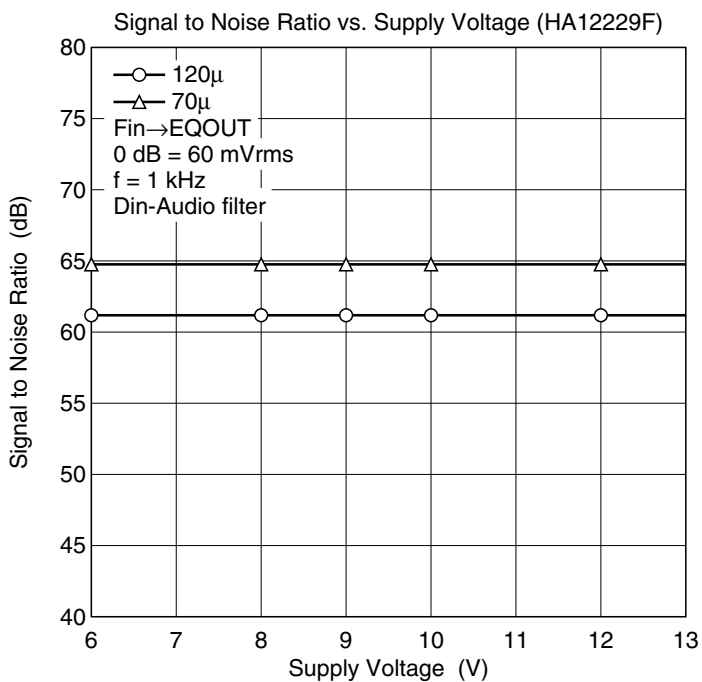


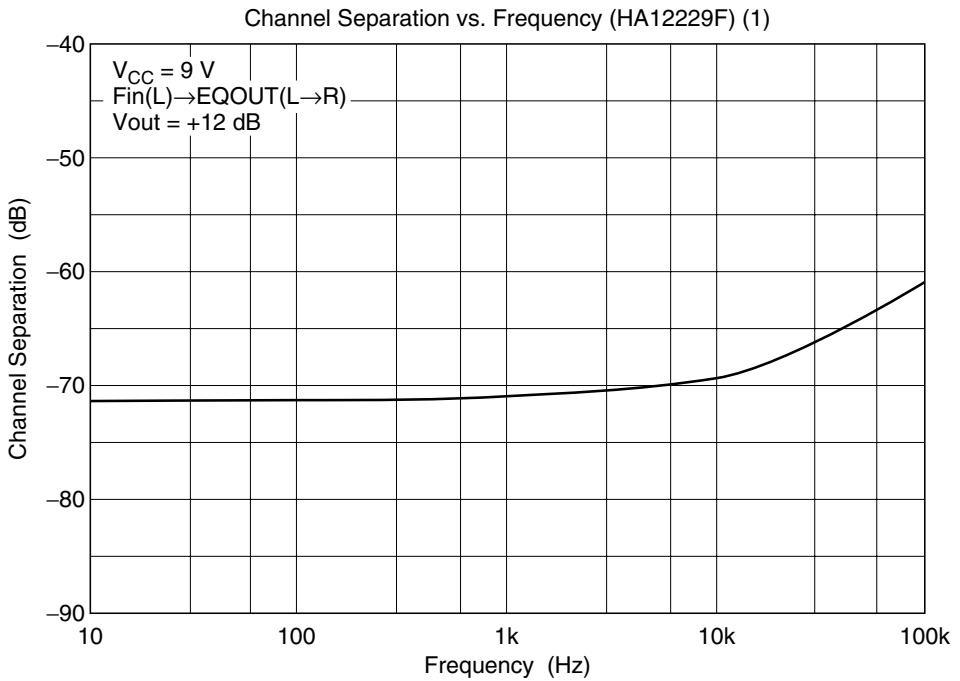
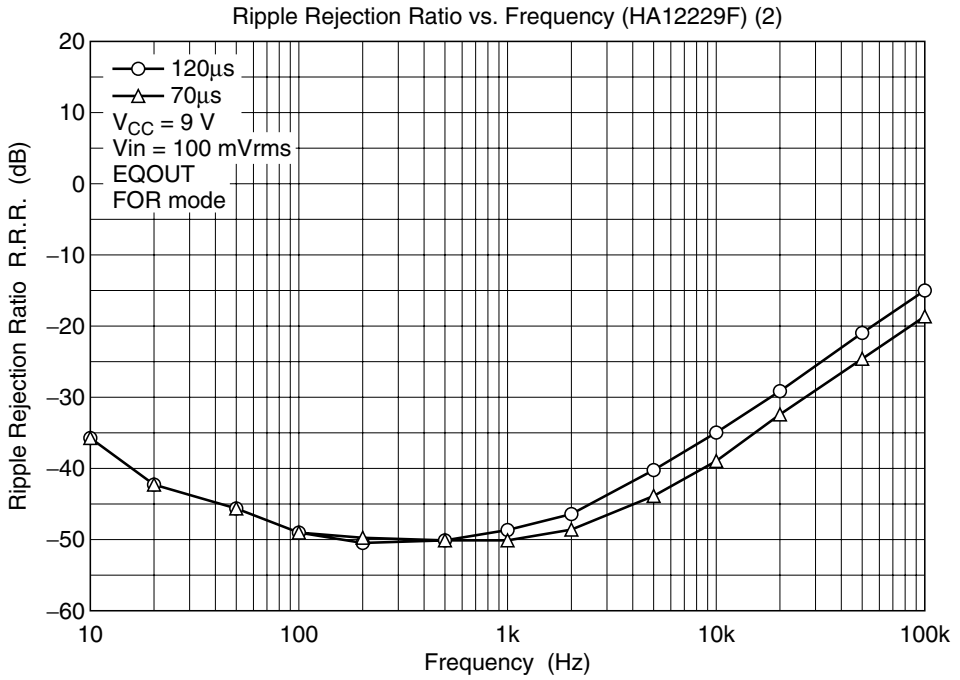
Signal Handling (HA12229F) (1)



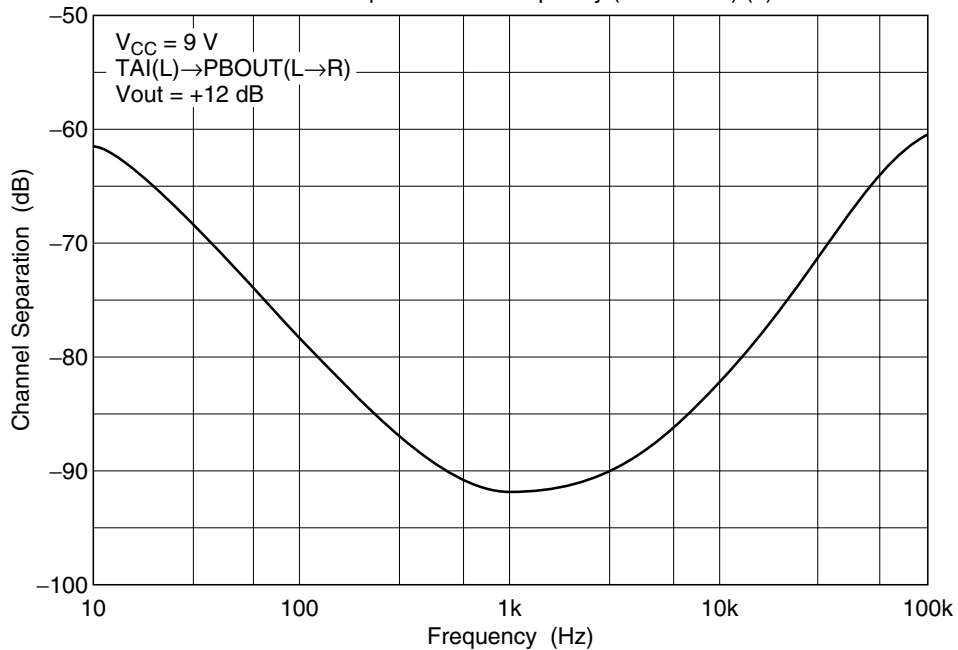
Signal Handling (HA12229F) (2)



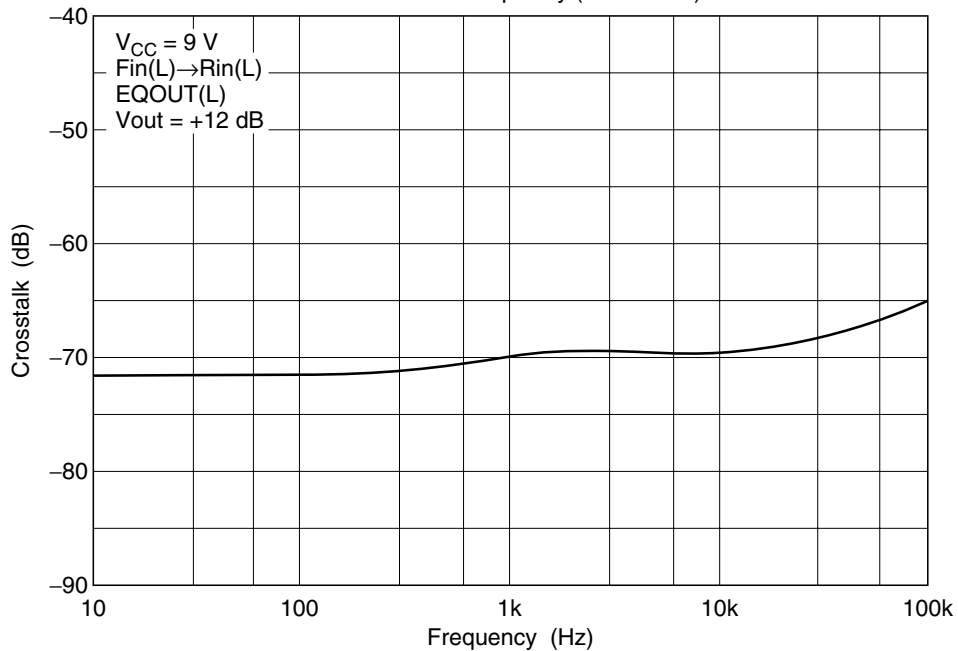




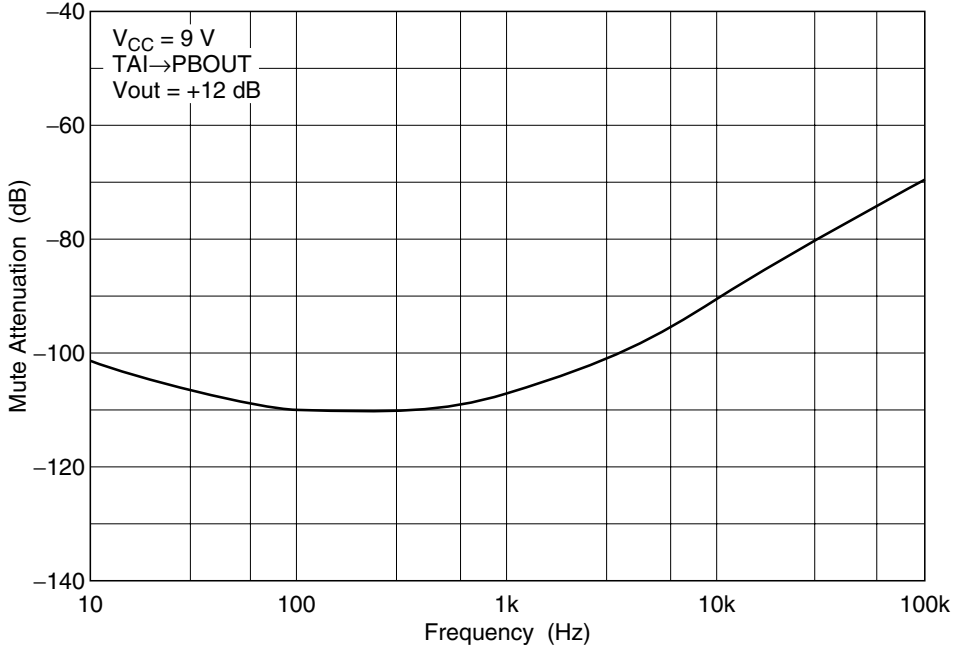
Channel Separation vs. Frequency (HA12229F) (2)



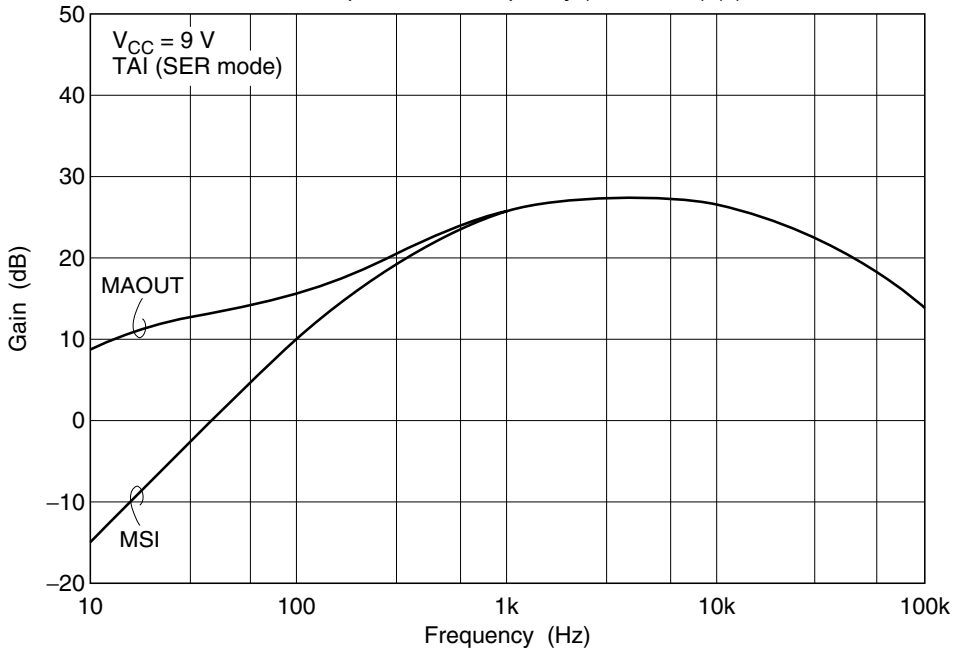
Crosstalk vs. Frequency (HA12229F)



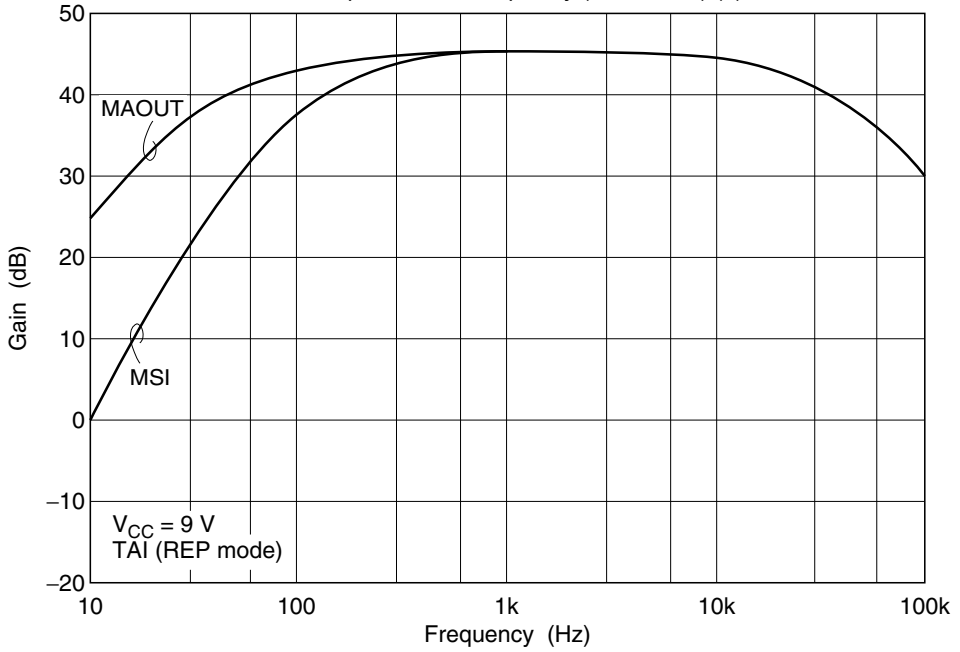
Mute Attenuation vs. Frequency (HA12229F)



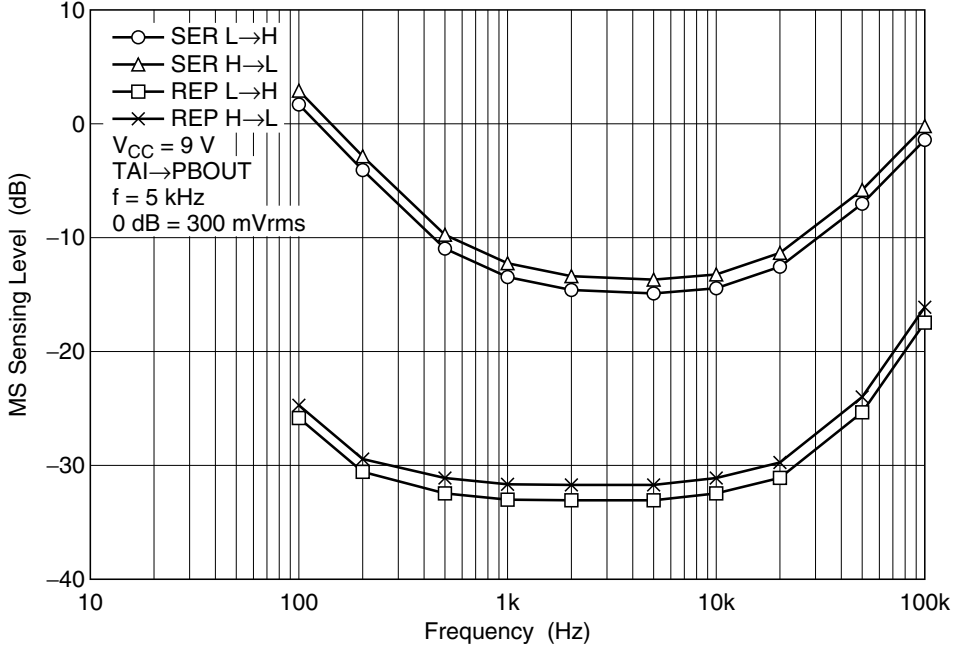
MS Amp. Gain vs. Frequency (HA12229F) (1)



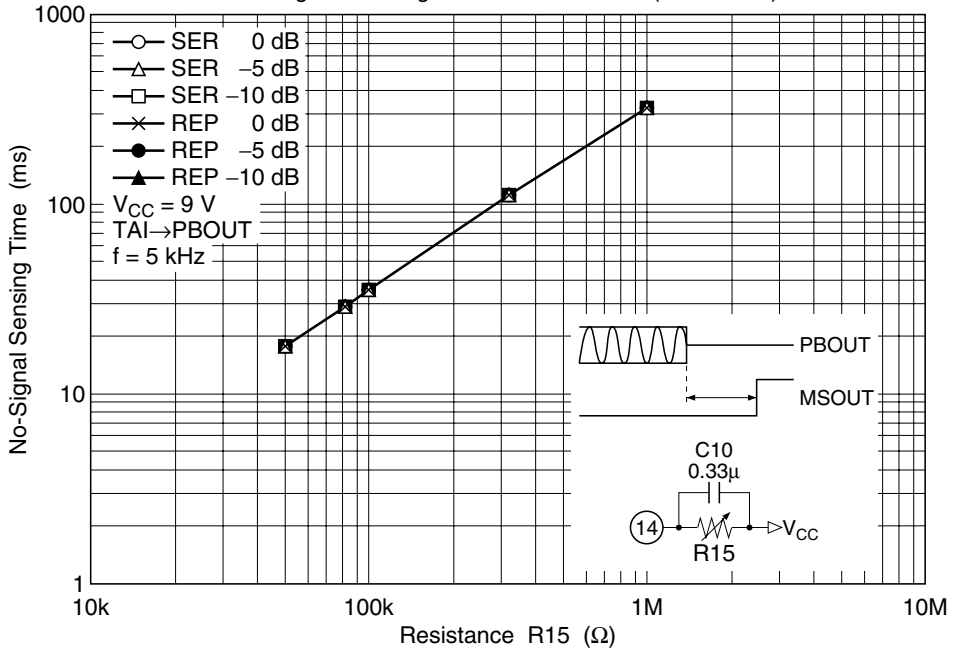
MS Amp. Gain vs. Frequency (HA12229F) (2)



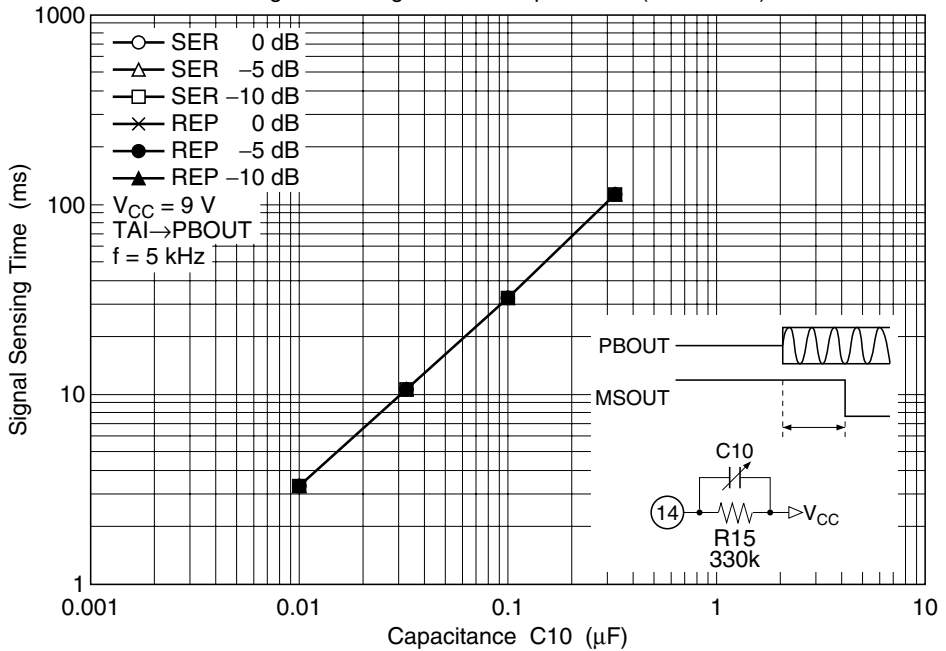
MS Sensing Level vs. Frequency (HA12229F)



No-Signal Sensing Time vs. Resistance (HA12229F)

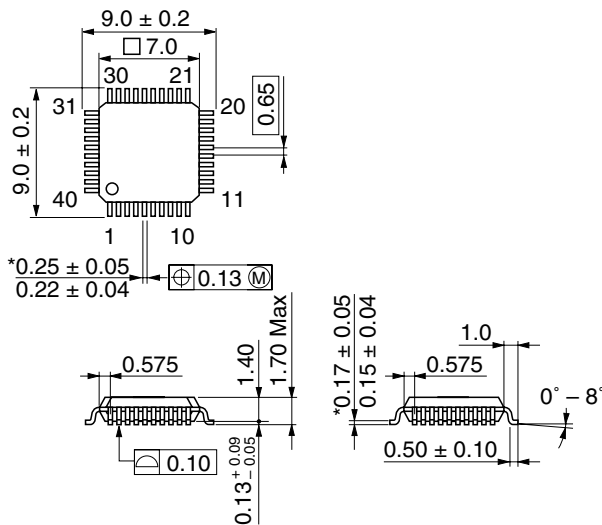


Signal Sensing Time vs. Capacitance (HA12229F)



Package Dimensions

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-40B
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.2 g

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